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Tse et al.

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(54) **HIGH VOLTAGE SEMICONDUCTOR POWER SWITCHING DEVICE**

USPC 257/140, 337, 477, 570; 438/127
See application file for complete search history.

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(56) **References Cited**

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U.S. PATENT DOCUMENTS

7,358,968	B2 *	4/2008	Sasada et al.	345/204
8,581,339	B2 *	11/2013	Chang et al.	257/335
2011/0012130	A1 *	1/2011	Zhang	257/77
2012/0049831	A1 *	3/2012	Tse et al.	323/299
2012/0256229	A1 *	10/2012	Chen	257/139
2013/0341729	A1 *	12/2013	Hisamoto et al.	257/378
2014/0146575	A1 *	5/2014	Tse et al.	363/20

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* cited by examiner

(*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 10 days.

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H01L 29/66 (2006.01)

H01L 27/06 (2006.01)

(52) **U.S. Cl.**

CPC **H01L 27/0647** (2013.01); **H01L 27/0635** (2013.01); **H01L 2224/48137** (2013.01); **H01L 2224/48247** (2013.01); **H01L 2224/49171** (2013.01); **H01L 2924/13055** (2013.01)

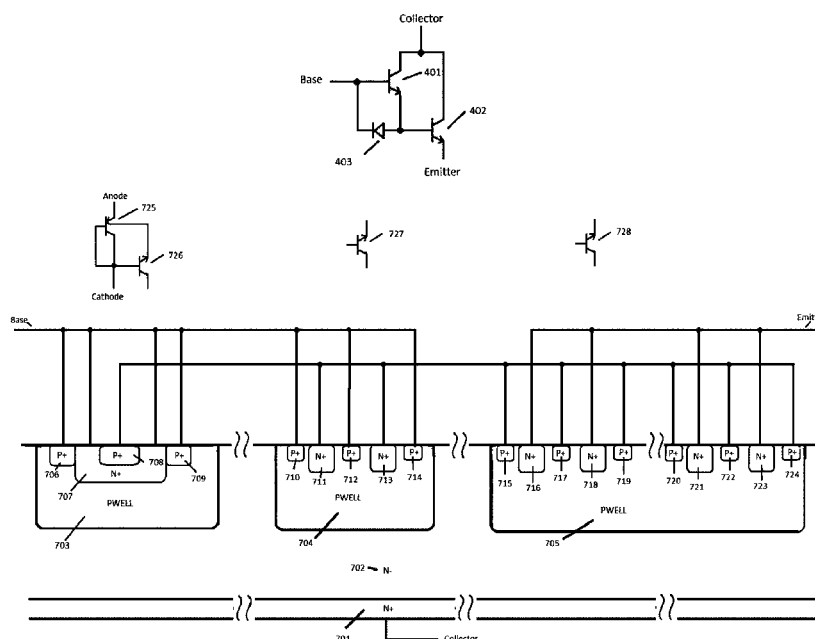
(58) **Field of Classification Search**

CPC H01L 27/06; H01L 21/56; H01L 29/739; H01L 29/872

(57) **ABSTRACT**

A three terminal high voltage Darlington bipolar transistor power switching device includes two high voltage bipolar transistors, with collectors connected together serving as the collector terminal. The base of the first high voltage bipolar transistor serves as the base terminal. The emitter of the first high voltage bipolar transistor connects to the base of the second high voltage bipolar transistor (inner base), and the emitter of the second high voltage bipolar transistor serves as the emitter terminal. A diode has its anode connected to the inner base (emitter of the first high voltage bipolar transistor, or base of the second high voltage bipolar transistor), and its cathode connected to the base terminal. Similarly, a three terminal hybrid MOSFET/bipolar high voltage switching device can be formed by replacing the first high voltage bipolar transistor of the previous switching device by a high voltage MOSFET.

12 Claims, 19 Drawing Sheets



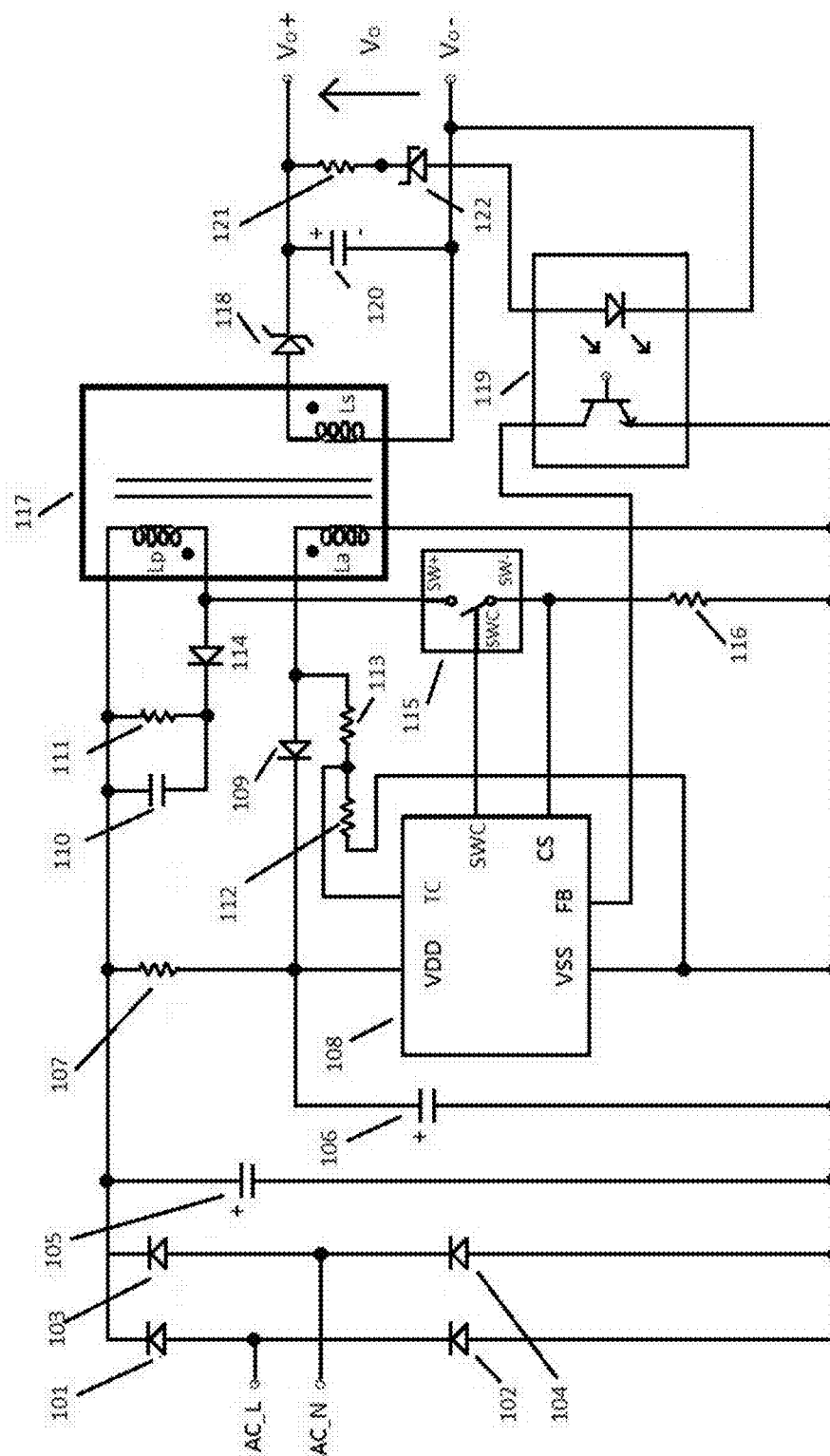


Fig 1. (Prior Art)

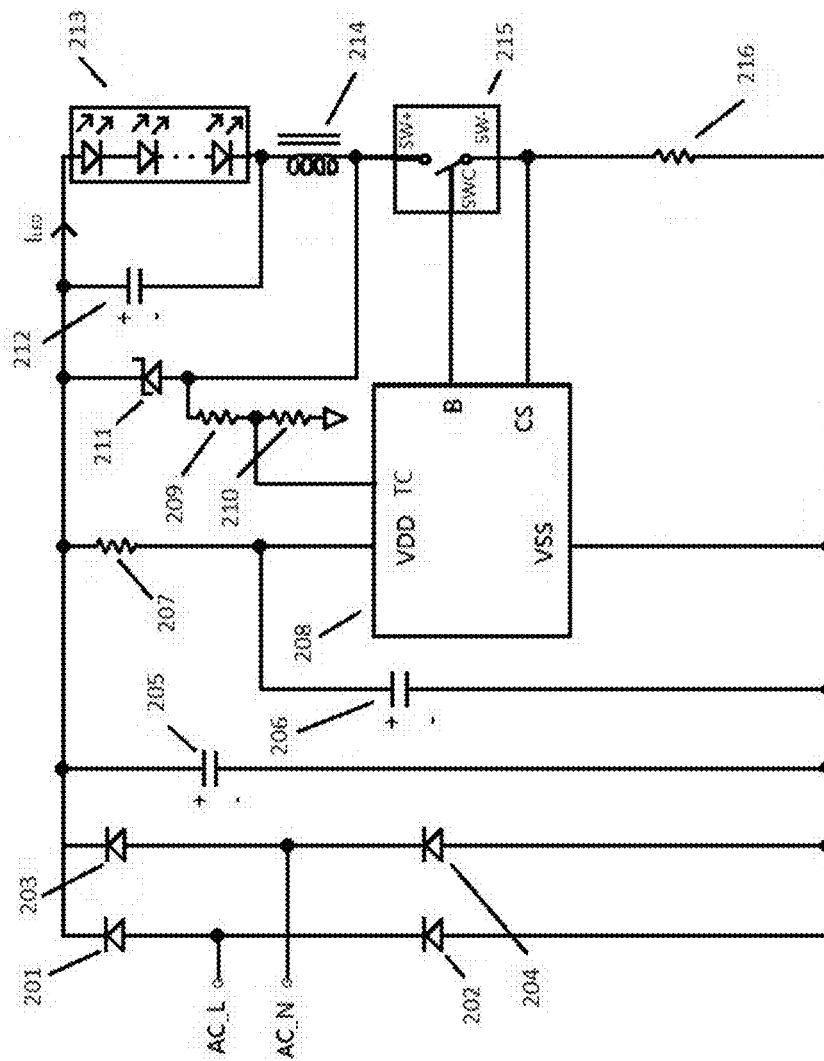


Fig. 2 (Prior Art)

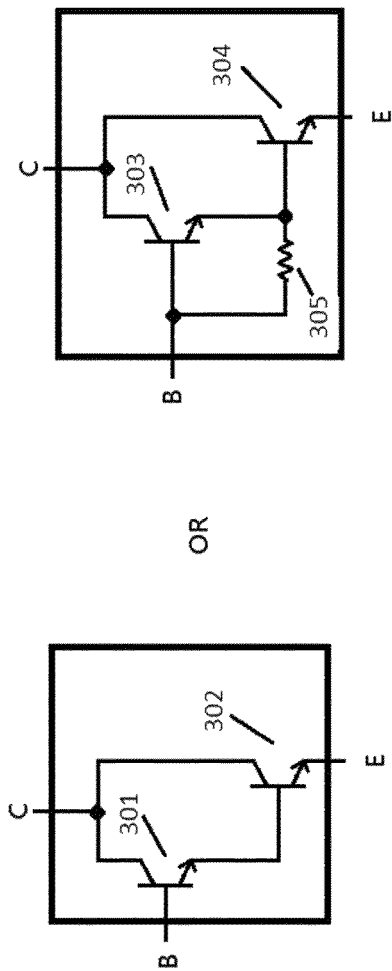


Fig. 3 (Prior Art)

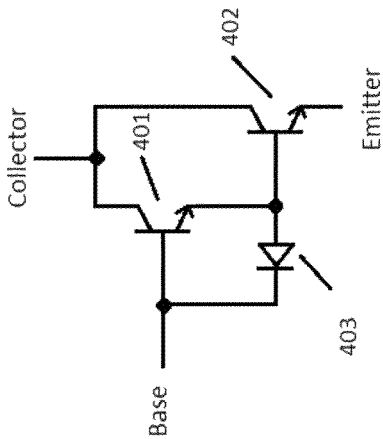


Fig. 4

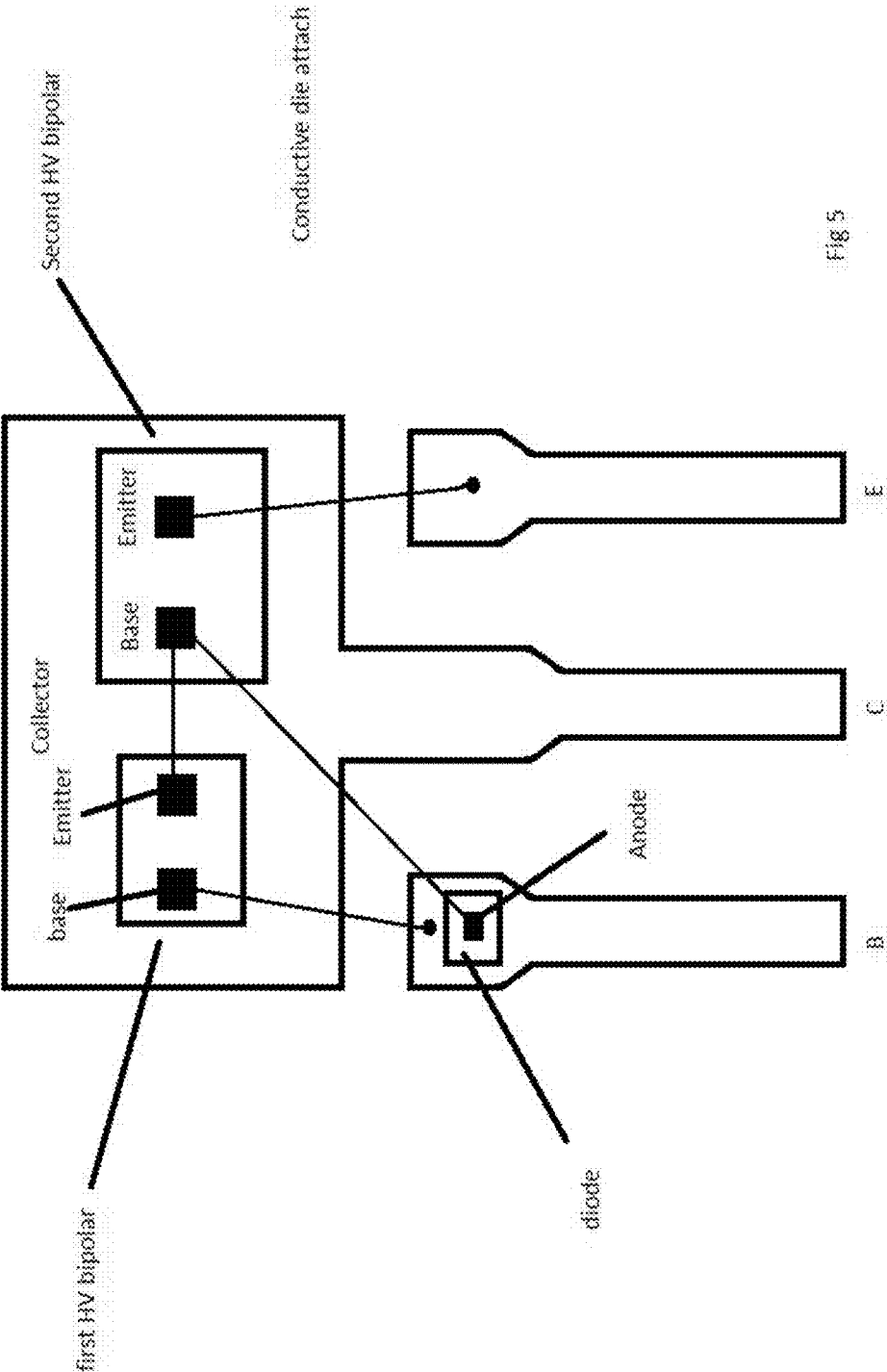
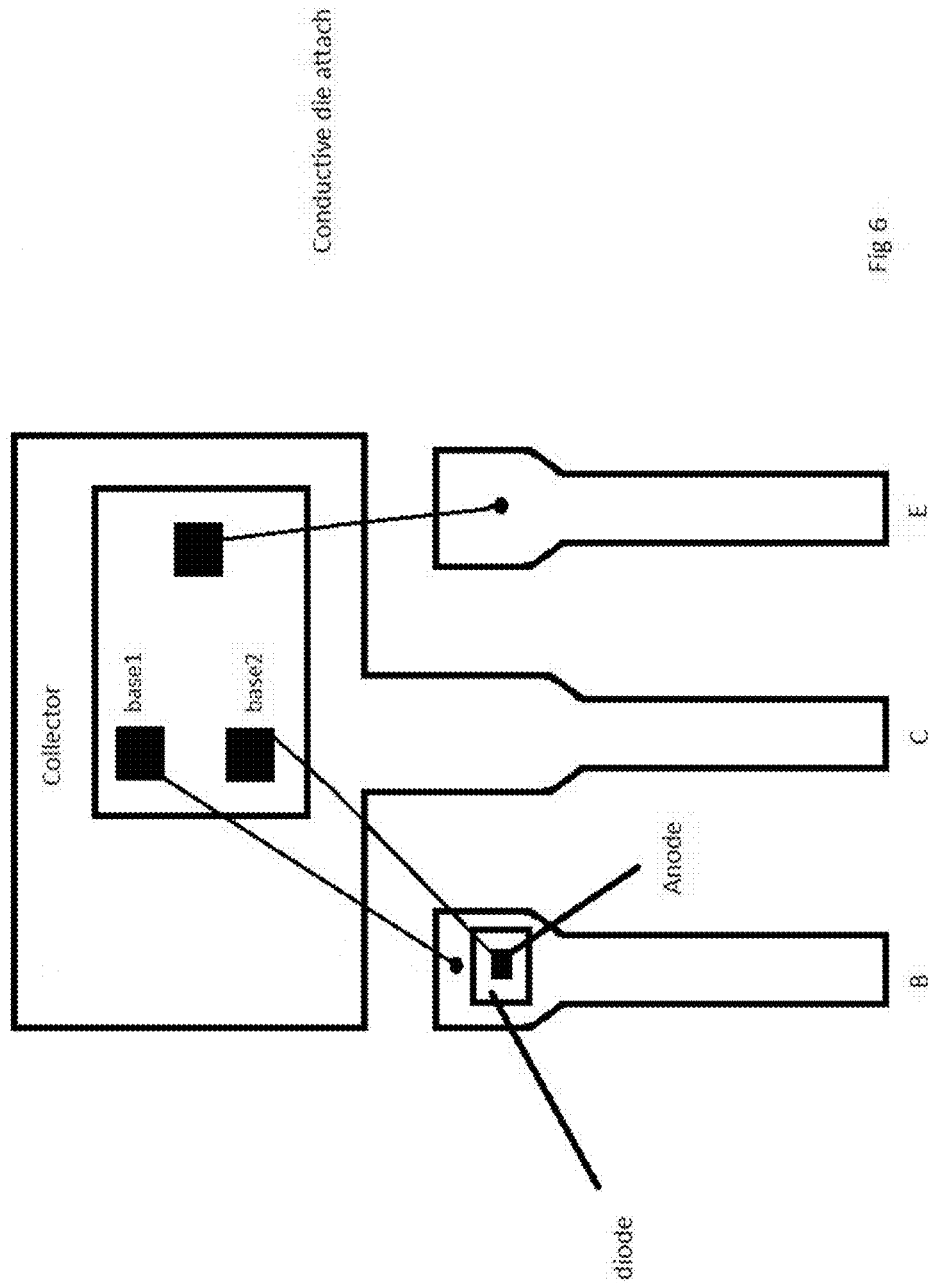


Fig 5



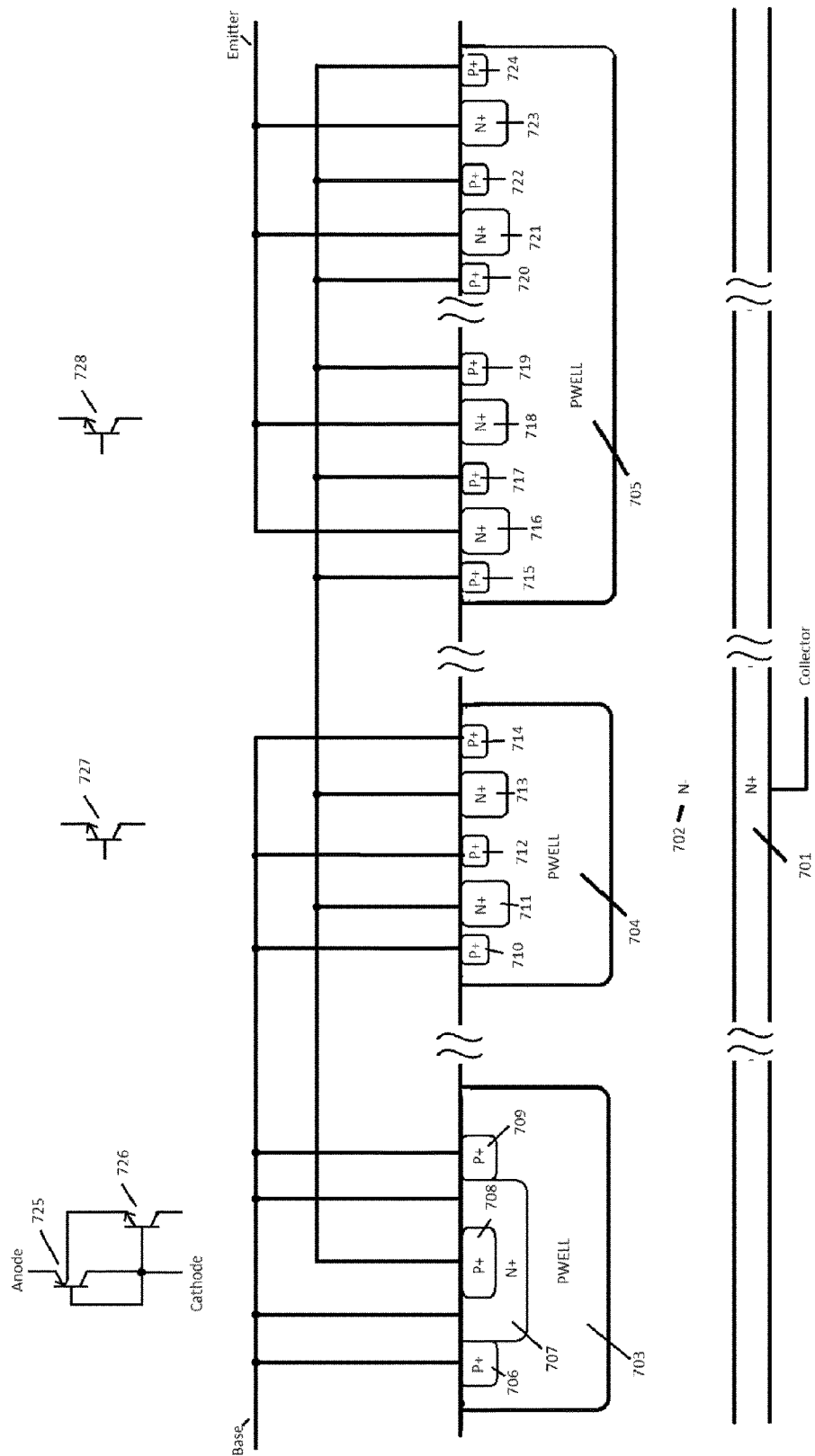


Fig. 7

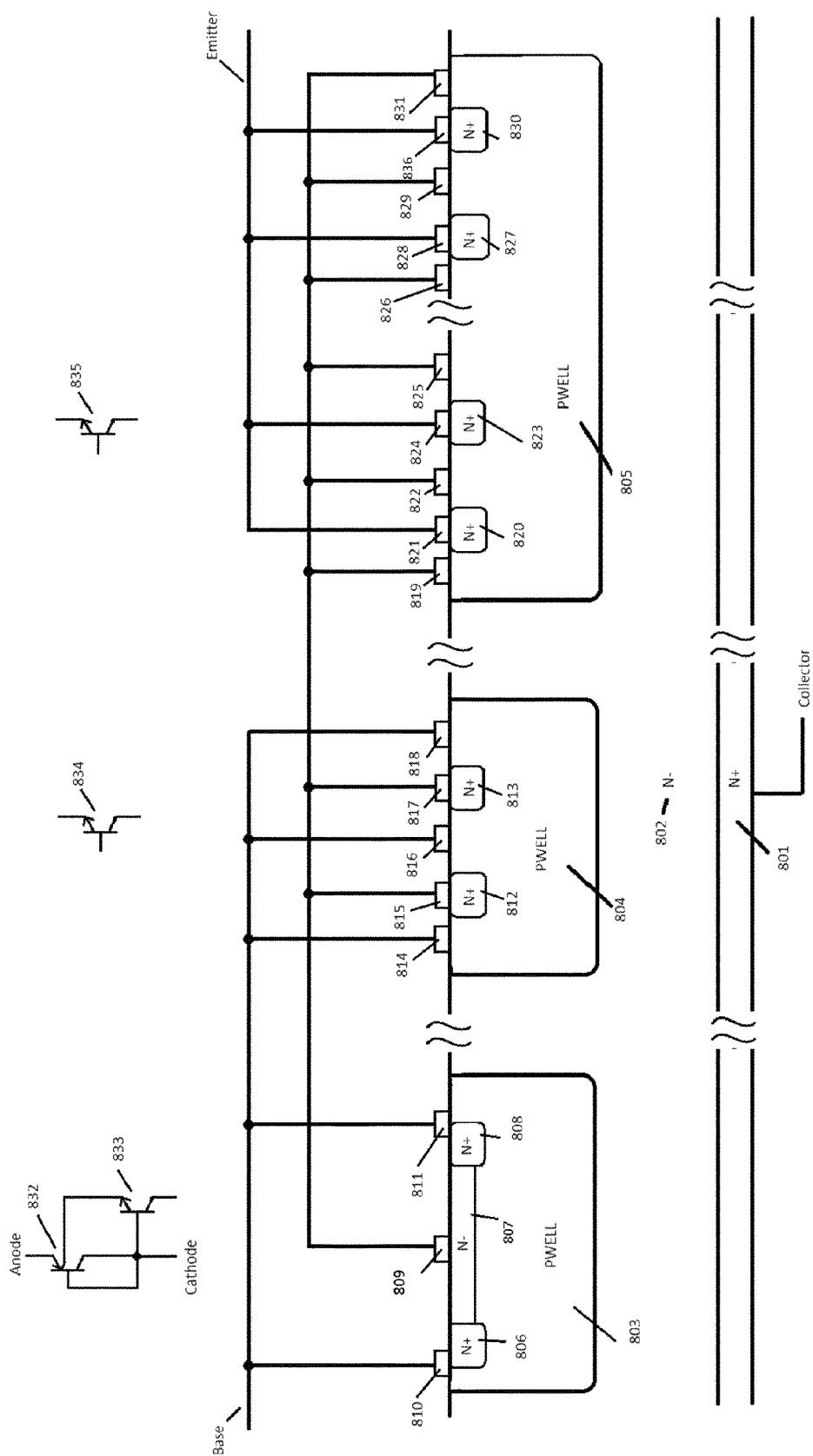


Fig. 8

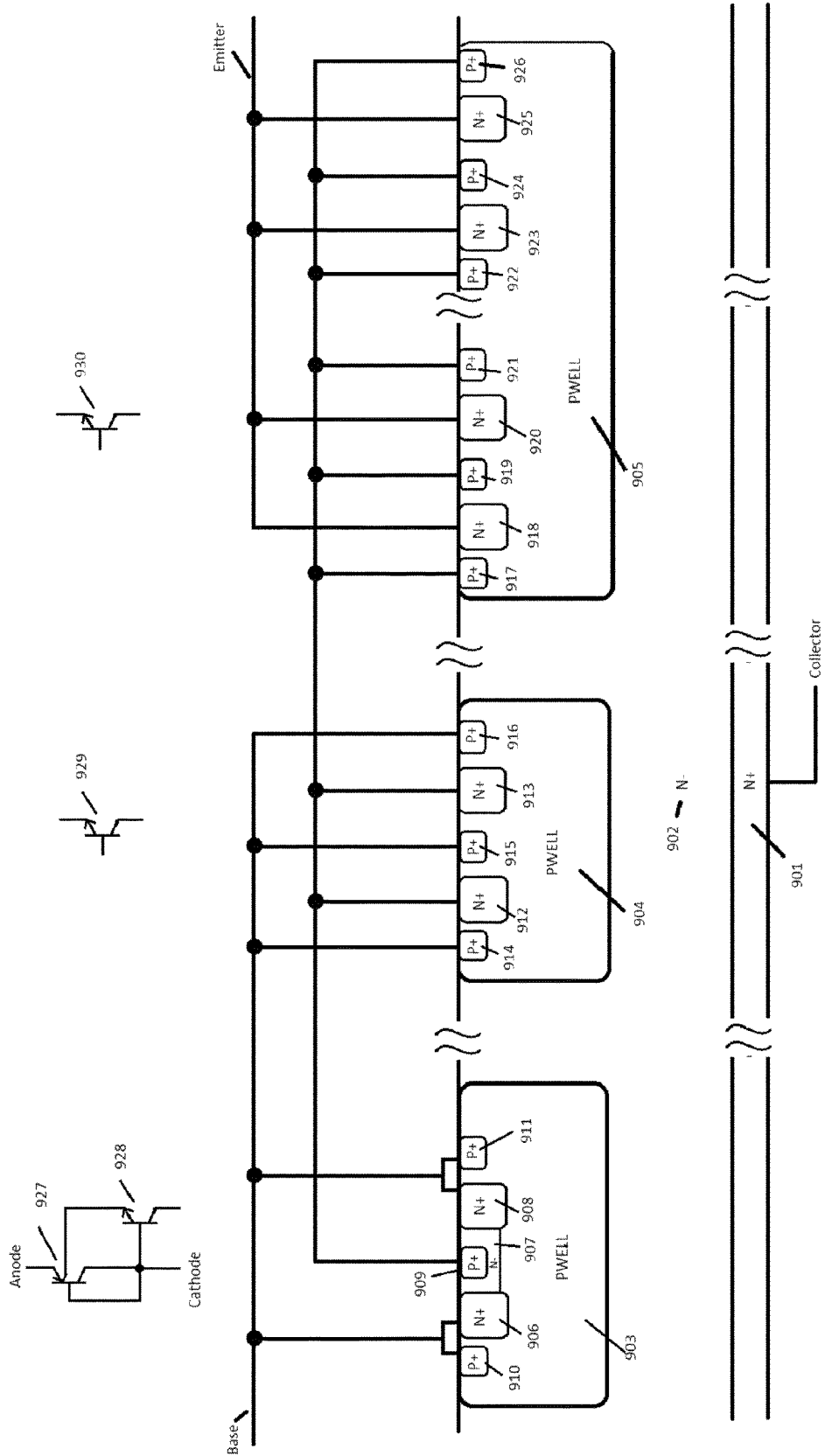
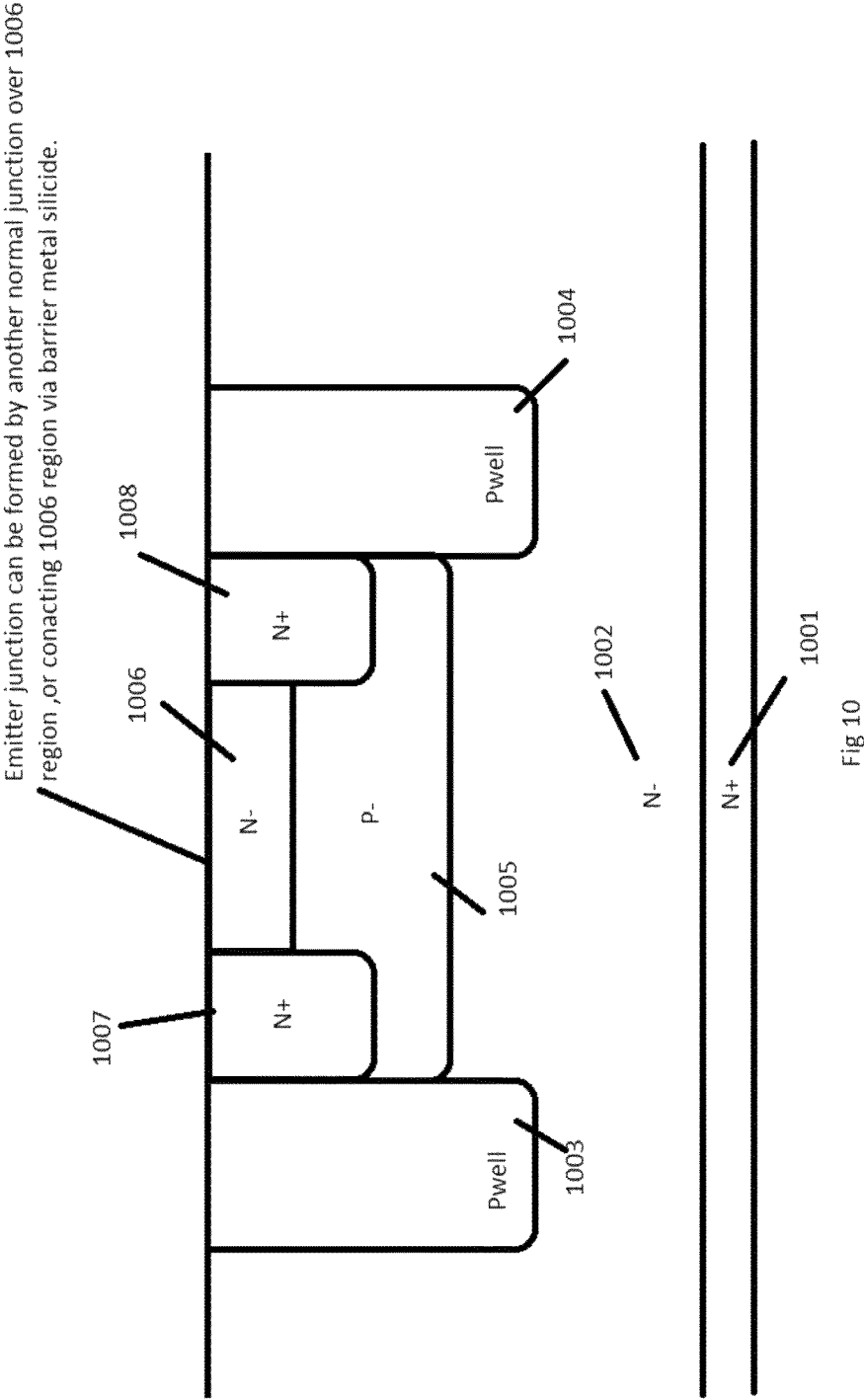


Fig 9



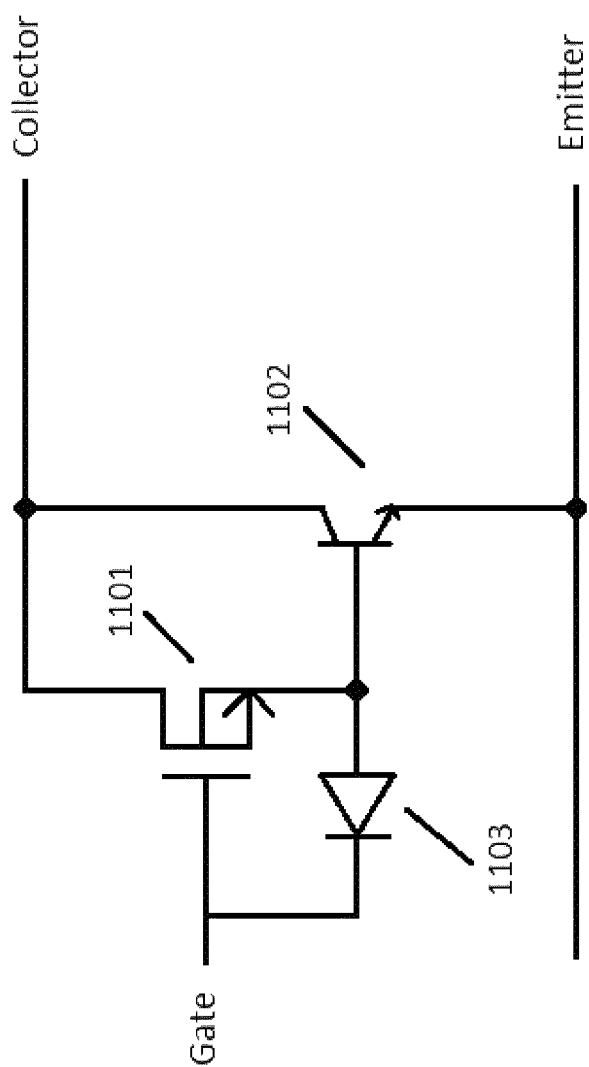


Fig 11

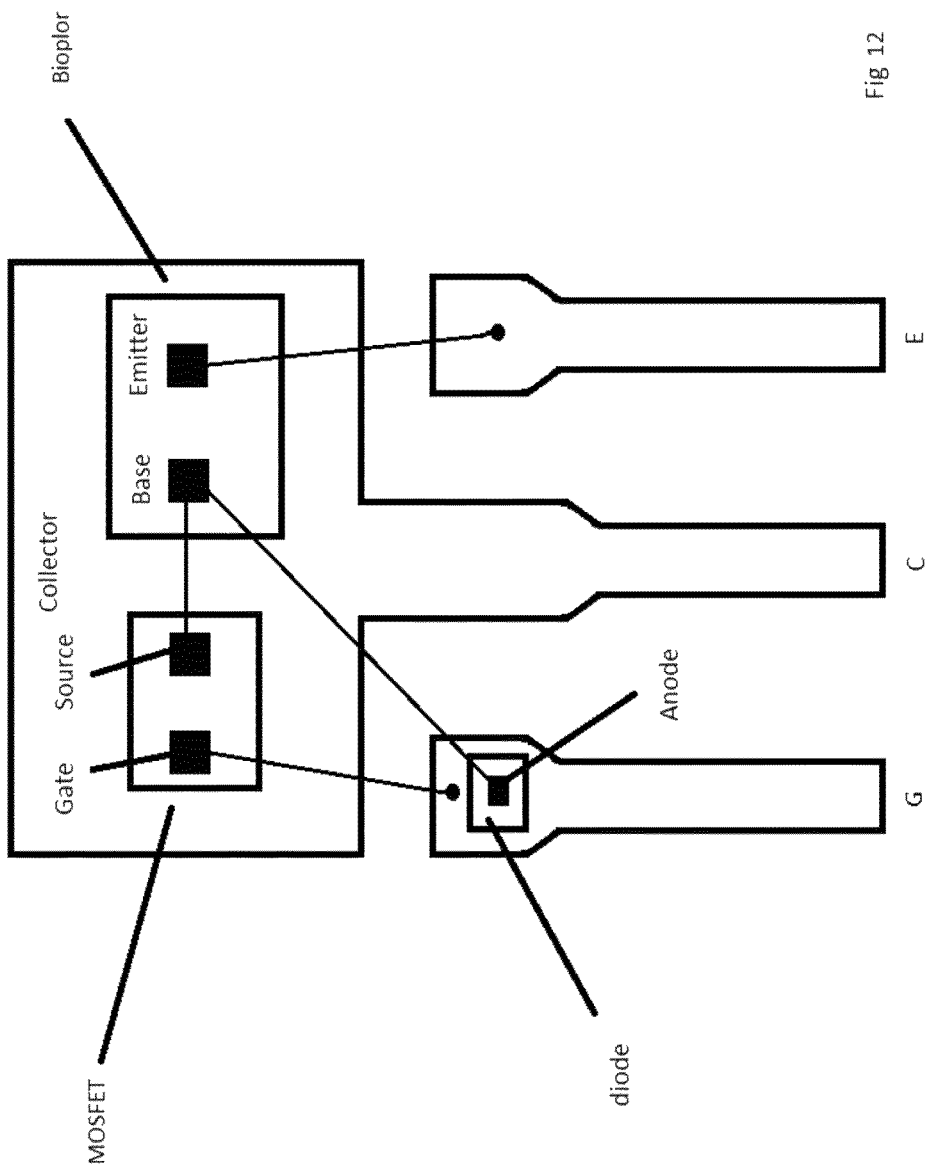


Fig 12

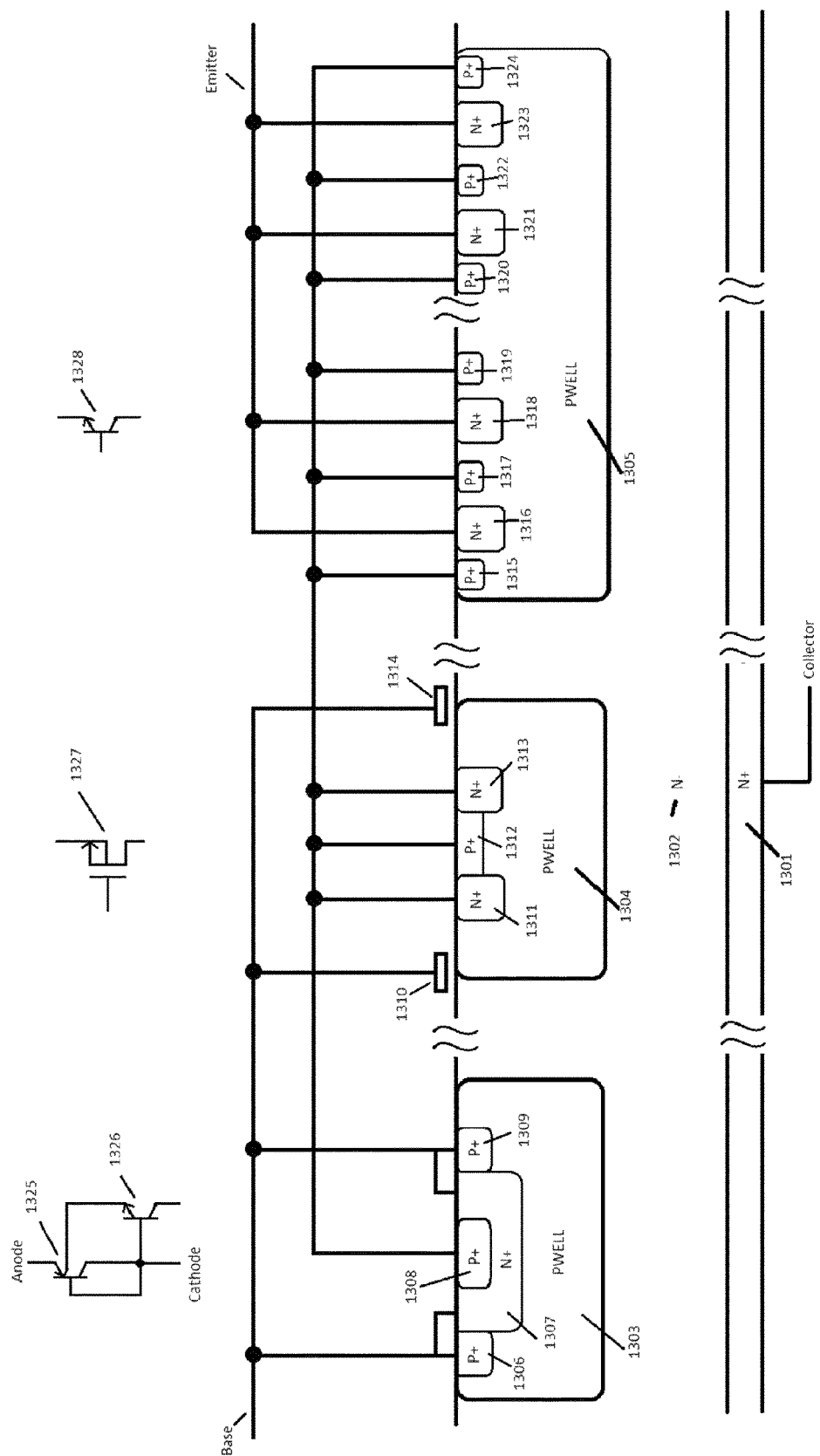
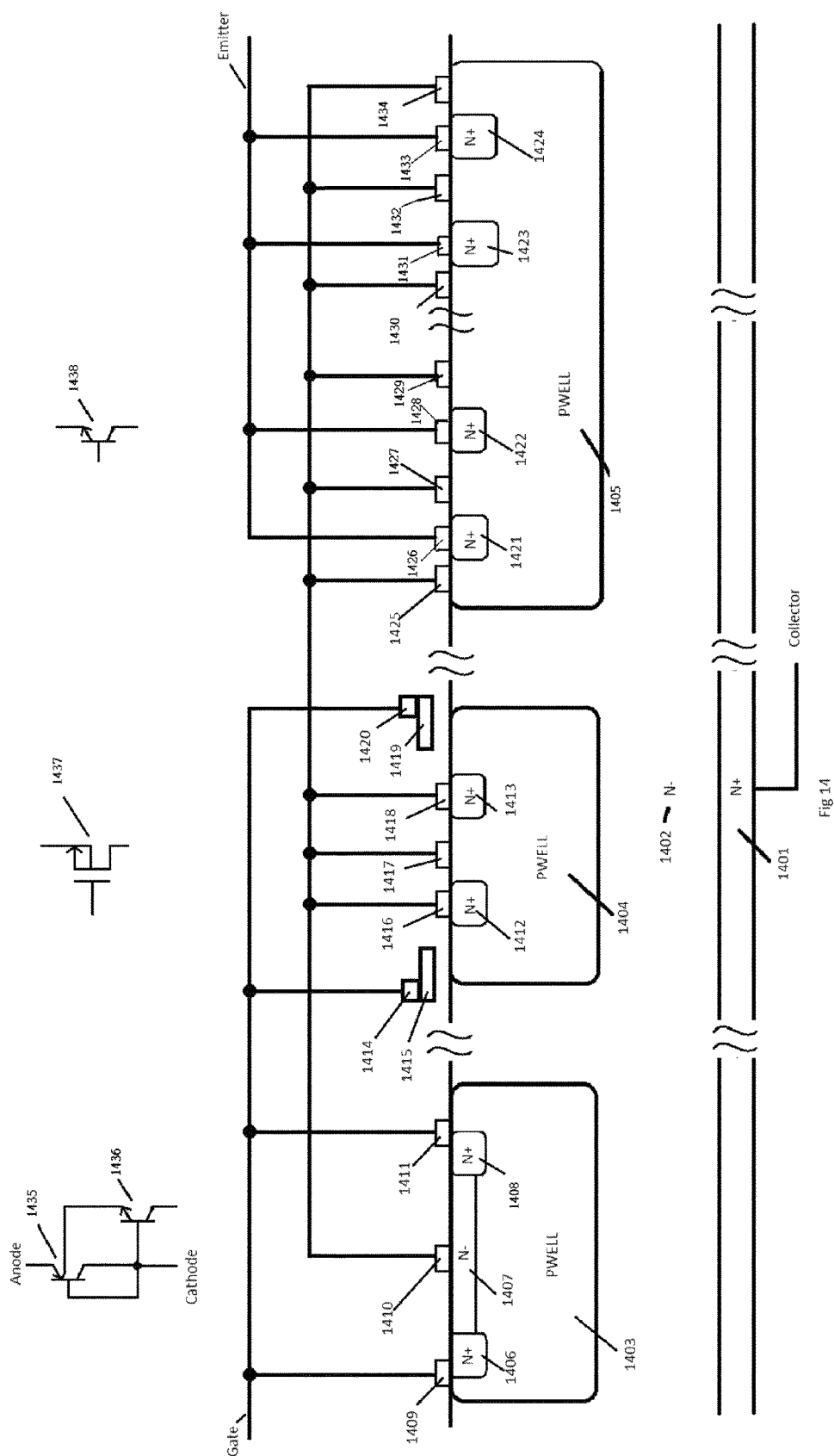


Fig 13



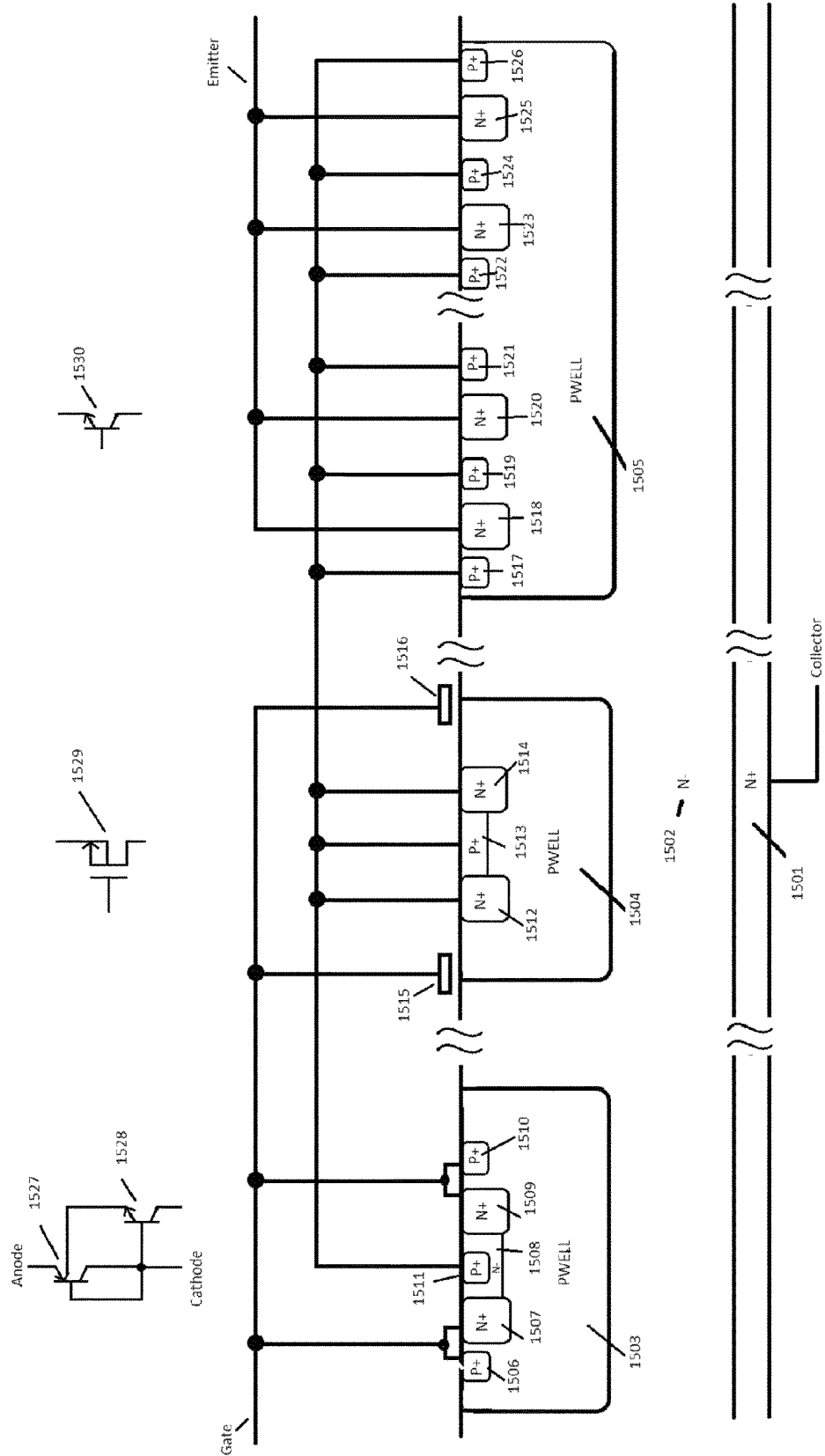


Fig 15

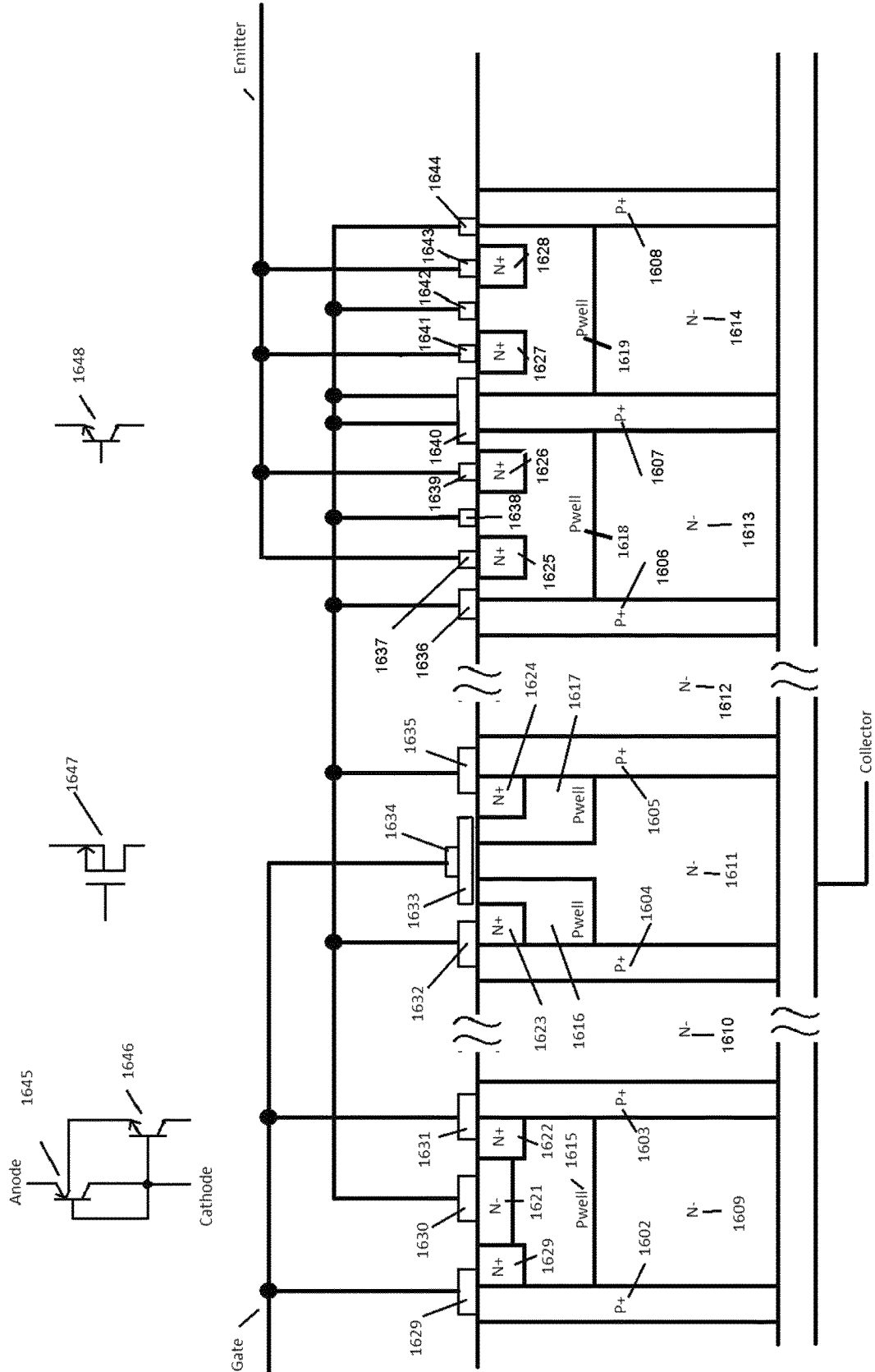
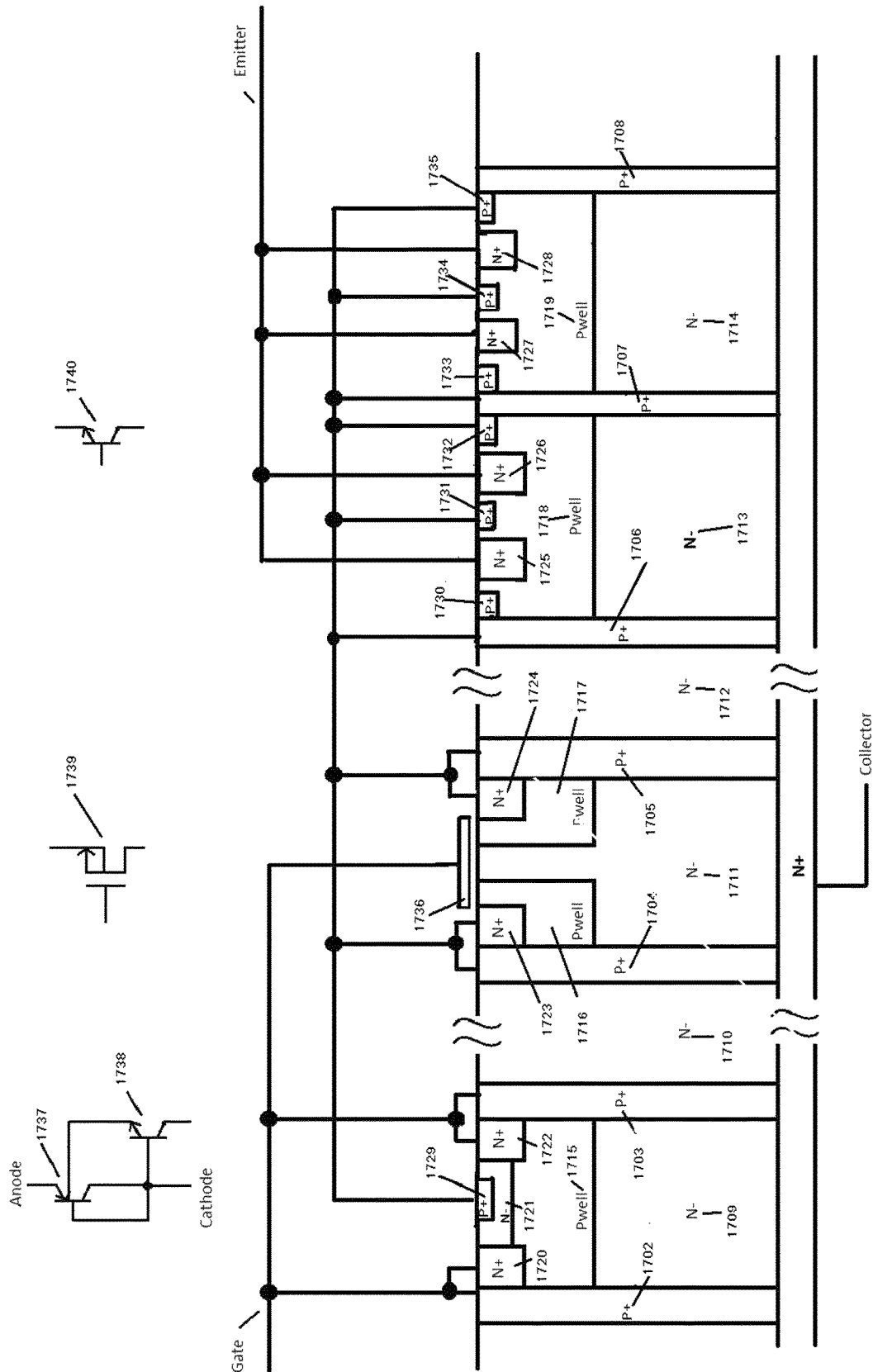
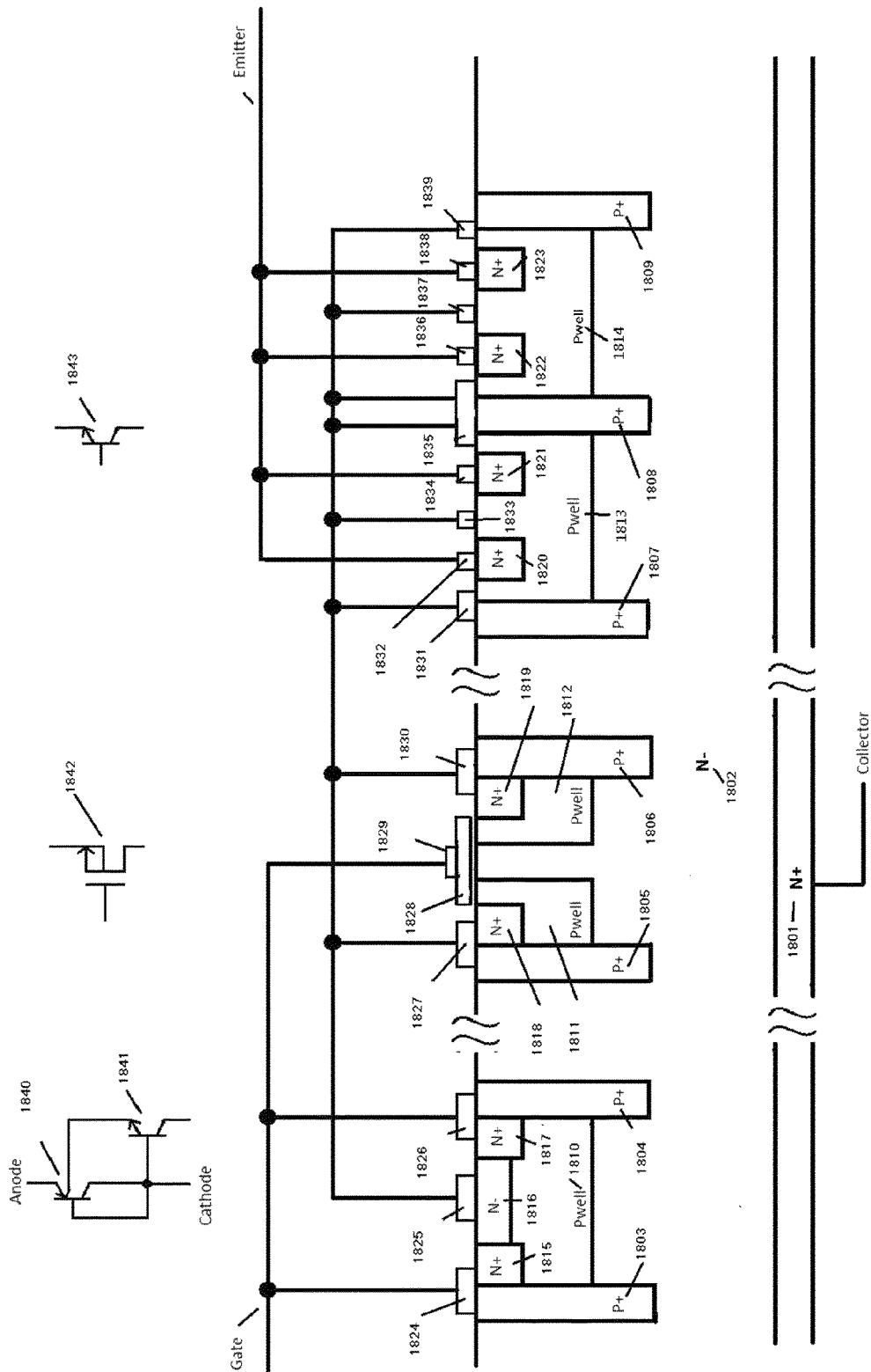


FIG 16





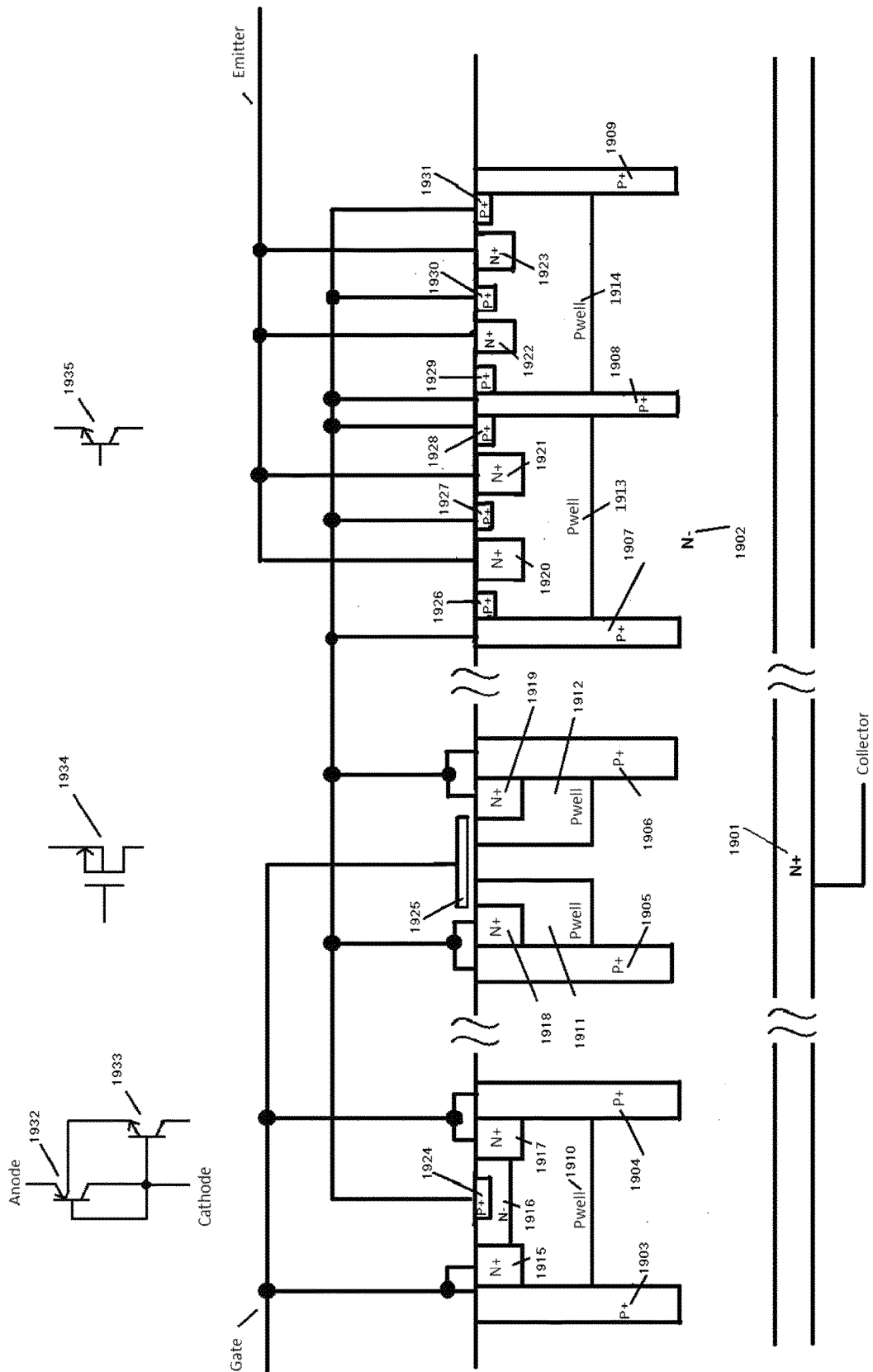


FIG 19

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HIGH VOLTAGE SEMICONDUCTOR POWER SWITCHING DEVICE

BACKGROUND OF THE INVENTION

The present invention relates to high voltage semiconductor switching devices. The invention more particularly, although not exclusively, relates to switching device for switching converter applications.

Prior art switching converter circuits are shown in FIGS. 1 and 2. FIG. 1 shows an isolated constant voltage output switching converter while FIG. 2 shows a non-isolated switching converter having constant current output for driving LED lighting.

In both FIGS. 1 and 2, the selection of the power switching device (115 and 215 respectively) is a key decision. Bipolar transistor and MOSFET are typical candidates for power switching device. Bipolar transistors are much less costly than the MOSFET at the same power rating. However, MOSFETs are normally more preferred, especially at high power levels, due to the following reasons:

- a. Bipolar transistors require continuous base current to keep them in the turn on state while MOSFETs only require the charge up of the gate capacitance to turn them on;
- b. The current gain for power bipolar transistors with high breakdown voltage (say, 600V or more) is usually not high (say, at around 10 to 20, or even less than 10). This renders the power for driving the base substantial, especially when the power converter delivers high power to its output. The efficiency of the switching converter circuit will then be degraded.

By using bipolar transistors in a Darlington configuration, effective current gain becomes product of individual transistor current gain. Hence, effective current gain of a few hundred can be obtained easily and the power loss due to base driving can be reduced to comparable with the gate driving for MOSFET counterpart at the same power level. However, commercially available Darlington transistors are normally being offered in three pin package in which B is the first base and E is the last emitter as shown in FIG. 3. It is easy to turn on by a small base current but the turn off is very slow due to base relaxation at the inner base (base pin for transistors 302 and 304 in FIG. 3). Therefore, it is not suitable for switching converter application as slow switching transition generates substantial amount of heat at the switching device, as well as degradation of efficiency.

IGBT is a hybrid power switching device that attempts to combine the advantage of MOSFET and bipolar transistor. For IGBT, the power for the gate driving is small as it is the charge up of the control gate capacitance similar to the case of MOSFET while the chip size is similar to bipolar transistor for the same rated current due to the conduction mode is bipolar action. However, due to the actual bipolar base terminal is inside the device, it suffers the same problem of slow switching off as the three terminal Darlington bipolar transistor.

As of today, MOSFET is still the most widely used choice for power switching device.

SUMMARY

A high voltage three pin Darlington bipolar power switching device with fast turn off time is provided.

A high voltage hybrid MOSFET/bipolar power switching device with fast turn off time is also provided.

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Each of these power switching devices can be fabricated as monolithic devices.

There is disclosed herein a three terminal high voltage Darlington bipolar transistor power switching device including the following components:

two high voltage bipolar transistors, with collectors connected together serving as the collector terminal for the power switching device, the base of the first high voltage bipolar transistor serving as the base terminal of the power switching device, the emitter of the first high voltage bipolar transistor connecting to the base of the second high voltage bipolar transistor (inner base), and the emitter of the second high voltage bipolar transistor serving as the emitter terminal of the power switching device; and

a diode with its anode connected to the inner base (emitter of the first high voltage bipolar transistor, or base of the second high voltage bipolar transistor), and its cathode connected to the base terminal of the power switching device.

Preferably, the diode is a Schottky diode.

Alternatively, the diode can take the form of a diode connector bipolar transistor.

Preferably, all components are integrated as a monolithic IC using high voltage SOI process.

Preferably, all components are integrated as a monolithic IC using modified high voltage planer process.

There is further disclosed herein a method of fabricating a three terminal high voltage Darlington bipolar power switching including the steps of:

conductive die attaching two high voltage bipolar transistors having the substrate as collector terminal to the main die pad of a three pin power device package, which serves as the collector terminal for the power switching device;

conductive die attaching a diode with cathode as substrate to the base bonding pin of the base terminal of the three pin power device package;

bonding the base of the first high voltage bipolar transistor to the base terminal of the three pin power device package;

inter-chip bonding of the emitter of the first high voltage bipolar transistor to the base of the second high voltage bipolar transistor;

bonding of the emitter of the first high voltage bipolar transistor and/or the base of the second high voltage bipolar transistor to the anode of the diode;

bonding of the emitter of the second high voltage bipolar transistor to the emitter pin of the three pin power package; and

subsequent standard moulding and follow on process to complete the device packaging.

The diode can be a Schottky diode.

There is further disclosed herein a method of fabricating a three terminal high voltage Darlington bipolar power switching device including the steps of:

conductive die attaching a single semiconductor chip high voltage Darlington bipolar transistor having four terminals—namely collector, first base, inner base, and emitter, with the substrate as the collector terminal, to the main die pad of a three pin power device package, which is also electrically connected to the collector terminal of the package;

conductive die attaching a diode with cathode as substrate to the base bonding pin of the base terminal of the three pin power device package;

bonding the first base of the high voltage Darlington bipolar transistor to the base terminal of the three pin power device package;

bonding the inner base of the high voltage Darlington bipolar transistor to the anode of the diode;

bonding the emitter of the high voltage Darlington bipolar transistor to the emitter pin of the three pin power package; and

subsequent standard moulding and follow on process to complete the device packaging.

Again, the diode can be a Schottky diode.

There is further disclosed herein a monolithic three terminal high voltage Darlington bipolar power switching semiconductor integrated circuit including:

two high voltage bipolar transistors, with their substrates as a common collector and also serving as the collector terminal of the power switching integrated circuit at the back side;

two semiconductor well regions with the opposite dopant type to the substrate serving as the base regions for the high voltage bipolar transistors;

high doping density semiconductor electrodes of the same type as the substrate inside the base regions serving as emitters for the high voltage bipolar transistors; wherein:

the base of the first high voltage bipolar transistor serves as the base terminal of the power switching integrated circuit;

the emitter of the first high voltage bipolar transistor connects to the base of second high voltage bipolar transistor (inner base);

the emitter of the second high voltage bipolar transistor serves as the emitter terminal of the power switching integrated circuit; and

a diode with its anode connected to the inner base and its cathode connected to the base terminal of the power switching integrated circuit; wherein

the diode is a diode connected bipolar transistor with the following:

its collector as a well with opposite dopant type to the substrate on the substrate of the high voltage bipolar transistors;

a base inside the collector well with dopant type different from that of the collector well and interconnected to other components via electrodes;

an emitter, either as a semiconductor of the same type as the collector (for a normal diode), or as barrier metal silicide (for a Schottky diode); and

the base and collector terminals being mutually connected and serving as the cathode while the emitter serves as the anode of the diode.

Preferably, the collector well for the diode connected bipolar shares the same mask for fabricating the wells for the base regions of the two high voltage bipolar transistors, or is a separate region fabricated by additional masking.

Preferably, the collector well of for the diode connected bipolar has high doping density regions guarding a low doping density region of the same type with a junction depth less than the high doping region, the high doping regions being used for withstanding the high breakdown voltage as well as connecting the low doping density collector well for making connection to other electrodes. The low doping density region is serving as the actual collector well inside which the base and emitter of the diode connected bipolar device are formed.

Preferably, the well for the collector of the diode connected bipolar transistor device is merged with the base of the first high voltage bipolar transistor (base pin of the three terminal high voltage Darlington bipolar power switching integrated circuit).

Preferably, connections to the base regions of the high voltage bipolar transistors forming the Darlington device and the collector region of the diode connected bipolar device using a normal base emitter junction are made via the same kind of semiconductor electrode for the anode of the diode.

Alternatively, the integrated circuit is monolithic and the diode connected bipolar has a Schottky base emitter junction and connections to the Schottky diode anode make direct contact thereto.

Preferably, connections to other semiconductor regions are made via barrier metal silicide for a monolithic power switching integrated circuit with a Schottky diode in the form of diode connected bipolar device.

There is further disclosed herein a three terminal high voltage hybrid MOSFET/bipolar transistor power switching device including the following:

a high voltage MOSFET and a high voltage bipolar transistor, with the channel terminals of the MOSFET connected to the collector and base terminals of the bipolar transistor respectively, the collector and emitter of the bipolar transistor serving as the collector and emitter terminals of the power switching device respectively, and the gate of the MOSFET serving as the gate terminal of the three terminal high voltage hybrid MOSFET/bipolar transistor power switching device; and

a diode with the anode connected to the base of the high voltage bipolar transistor, and the cathode connected to the gate terminal of the power switching device.

The diode can be a Schottky diode.

The diode can (less preferably) take the form of a diode connector bipolar transistor.

Preferably, all components are fabricated on a monolithic IC using a high voltage SOI process.

Preferably, all components are fabricated as a monolithic IC using a planer, super-junction, or semi-super-junction high voltage process.

There is further disclosed herein a method of fabricating a three terminal high voltage hybrid MOSFET/bipolar power switching device, including the steps of:

conductive die attaching a high voltage MOSFET and a high voltage bipolar transistor having the substrate as drain and collector terminal respectively, to the main die pad of a three pin power device package, which serves as the collector terminal for the power switching device;

conductive die attaching a diode with cathode as substrate to the gate bonding pin of the gate terminal of the three pin power device package;

bonding the gate of the high voltage MOSFET to the gate terminal of the three pin power device package;

inter-chip bonding of the source of the high voltage MOSFET to the base of the high voltage bipolar transistor;

bonding of the source of the high voltage MOSFET and/or the base of the high voltage bipolar transistor to the anode of the diode;

bonding of the emitter of the high voltage bipolar transistor to the emitter pin of the three pin power package; and

subsequent standard moulding and follow on process to complete the device packaging.

The diode can be a Schottky diode.

There is further disclosed herein a monolithic three terminal high voltage hybrid bipolar MOSFET/bipolar power switching semiconductor integrated circuit fabricated by high voltage planer process including:

a high voltage MOSFET and a high voltage bipolar transistor, with substrate as the drain and collector respectively such that the substrate serves as the collector terminal for the switching integrated circuit via high doping concentration region of the same type at the back side;

two semiconductor well regions with the opposite dopant type to the substrate serving as the body and base regions for the high voltage MOSFET and high voltage bipolar transistor respectively;

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semiconductor electrodes of the same dopant type as the substrate with high doping density inside the body and base regions serving as source and emitter for the high voltage MOSFET and high voltage bipolar transistors respectively;

poly-silicon thin oxide gate electrodes overlapping the body and the substrate regions serving as the gate for the MOSFET; wherein:

the gate of the high voltage MOSFET serves as the gate terminal for the power switching integrated circuit;

the source terminal of the high voltage MOSFET connecting to the base of the high voltage bipolar transistor;

the body of the high voltage MOSFET connecting either to the source of the high voltage MOSFET, or as an alternative, to the emitter of the high voltage bipolar transistor;

the emitter of the high voltage bipolar transistor serving as the emitter terminal for the power switching integrated circuit; and

a diode with the anode connected to the base of the high voltage bipolar transistor and the cathode connected to the gate terminal of the power switching integrated circuit; wherein:

the diode is a diode connected bipolar transistor with the following:

the collector with dopant type opposite to the main substrate as a well on the substrate of the high voltage bipolar transistor similar to the body of the high voltage MOSFET, or the base of the high voltage bipolar transistor;

a base inside the collector well with dopant type opposite from that of the collector well with interconnections to other parts via electrode similar to the emitter regions of the high voltage bipolar transistor, or the source of the high voltage MOSFET;

an emitter, either as semiconductor of the same type as the collector at much higher doping density (for a normal diode), or as barrier metal silicide (for Schottky diode); and

the base and collector terminal are connected and serve as the cathode while the emitter serves as the anode of the diode.

Preferably, the collector well of for the diode connected bipolar shares the same mask for fabricating the wells for the body and base regions of the high voltage MOSFET and high voltage bipolar transistor, or as a separate region fabricated by additional masking.

Preferably, the collector well of for the diode connected bipolar has high doping density regions guarding a low doping density region of the same type with a junction depth less than the high doping region. The high doping regions are used for withstanding the high breakdown voltage as well as connecting the low doping density collector well for making connection, the low doping density region serving as the actual collector well inside which the base and emitter of the diode connected bipolar device are formed.

Preferably, the wells for the body of the high voltage MOSFET and the base of the high voltage bipolar transistor are merged for the case in which the body of the MOSFET is electrically connected to the base of the high voltage bipolar transistor.

Preferably, the diode is a Schottky diode and connections to semiconductor regions other than the Schottky diode anode are made via barrier metal silicide.

Preferably, connections to base region of the high voltage bipolar transistor and the body region of the high voltage MOSFET, and the collector region of the diode connected bipolar device using a normal base emitter junction are made via the same kind of semiconductor electrode for the anode of the diode.

There is further disclosed herein a monolithic three terminal high voltage hybrid bipolar MOSFET/bipolar power

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switching semiconductor integrated circuit fabricated by high voltage super-junction process including:

a high voltage MOSFET and a high voltage bipolar transistor, with substrate as the drain and collector respectively such that the substrate serves as the collector terminal for the power switching integrated circuit via high doping density region of the same type at the back side;

semiconductor well regions with the opposite dopant type to the substrate serving as the body and base regions for the high voltage MOSFET and high voltage bipolar transistor respectively, with high doping concentration super-junction columns of opposite type of dopant as the main substrate for withstanding the high breakdown voltage;

semiconductor electrodes of the same dopant type as the substrate with high doping density inside the body and base regions serving as source and emitter for the high voltage MOSFET and the high voltage bipolar transistor, respectively;

poly-silicon thin oxide gate electrodes overlapping the body and the substrate regions serving as the gate for the MOSFET; wherein:

the gate of the high voltage MOSFET serves as the gate terminal for the power switching integrated circuit;

the source terminal of the high voltage MOSFET connecting to the base of the high voltage bipolar transistor;

the body of the high voltage MOSFET connects to the source of the high voltage MOSFET, or as an alternative, to the emitter of the high voltage bipolar transistor;

the emitter of the high voltage bipolar transistor serves as the emitter terminal for the switching integrated circuit; and

a diode with the anode connected to the base of the high voltage bipolar transistor and the cathode connected to the gate terminal of the power switching integrated device; wherein

the diode is a diode connected bipolar transistor with the following:

the collector with dopant type opposite to the main substrate as a well on the substrate of the high voltage bipolar transistor similar to the body of the high voltage MOSFET, or the base of the high voltage bipolar transistor, with high doping concentration super-junction columns of opposite type of dopant of the substrate guarding the collector region for withstanding the high breakdown voltage;

a base inside the collector well with dopant type opposite from that of the collector well with interconnections to other parts via electrode similar to the emitter regions of the high voltage bipolar transistor, or the source of the high voltage MOSFET;

an emitter, either as semiconductor of the same type as the collector at much higher doping density (for a normal diode), or as a barrier metal silicide (for a Schottky diode); and

the base and collector terminal are connected and serves as the cathode while the emitter serves as the anode of the diode.

Preferably, the collector well for the diode connected bipolar shares the same mask for fabricating the wells for the body and base regions of the high voltage MOSFET and high voltage bipolar transistor, or as a separate region fabricated by additional masking.

Preferably, the collector well for the diode connected bipolar has high doping density regions guarding a low doping density region of the same type with a junction depth less than the high doping region. The high doping regions are used for withstanding the high breakdown voltage as well as connecting the low doping density collector well for making connection. The low doping density region is serving as the actual collector well inside which the base and emitter of the diode connected bipolar device are formed.

Preferably, the wells for the body of the high voltage MOSFET and the base of the high voltage bipolar transistor are merged for the case in which the body of the high voltage MOSFET is electrically connected to the base of the high voltage bipolar transistor. In addition, isolation region super-junction columns between the high voltage MOSFET and the high voltage bipolar transistor can also be merged, with the isolation region eliminated.

The diode can be a Schottky diode and connections to semiconductor regions other than the Schottky diode anode are made via barrier metal silicide.

Preferably, connections to base region of the high voltage bipolar transistor and the body region of the high voltage MOSFET, and the collector region of the diode connected bipolar device using normal base emitter junction are made via the same kind of semiconductor electrode for the anode of the diode.

There is further disclosed herein a monolithic three terminal high voltage hybrid bipolar MOSFET/bipolar power switching semiconductor integrated circuit fabricated by high voltage semi-super-junction process comprising:

a high voltage MOSFET and a high voltage bipolar transistor, with substrate as the drain and collector respectively such that the substrate serves as the collector terminal for the power switching integrated circuit via high doping density region of the same type at the back side;

semiconductor well regions with the opposite dopant type to the substrate serving as the body and base regions for the high voltage MOSFET and high voltage bipolar transistor respectively, with high doping concentration semi-super-junction columns of opposite type of dopant as the main substrate for withstanding the high breakdown voltage;

semiconductor electrodes of the same dopant type as the substrate with high doping density inside the body and base regions serving as source and emitter for the high voltage MOSFET and the high voltage bipolar transistor, respectively;

poly-silicon thin oxide gate electrodes overlapping the body and the substrate regions serving as the gate for the MOSFET; wherein:

the gate of the high voltage MOSFET serves as the gate terminal for the power switching integrated circuit;

the source terminal of the high voltage MOSFET connecting to the base of the high voltage bipolar transistor;

the body of the high voltage MOSFET connects to the source of the high voltage MOSFET, or as an alternative, to the emitter of the high voltage bipolar transistor;

the emitter of the high voltage bipolar transistor serving as the emitter terminal for the power switching integrated circuit; and

a diode with the anode connected to the base of the high voltage bipolar transistor and the cathode connected to the gate terminal of the power switching integrated circuit; wherein

the diode is a diode connected bipolar transistor with the following:

the collector with dopant type opposite to the main substrate as a well on the substrate of the high voltage bipolar transistor similar to the body of the high voltage MOSFET, or the base of the high voltage bipolar transistor, with high doping concentration semi-super-junction columns of opposite type of dopant of the substrate guarding the collector region for withstanding the high breakdown voltage;

a base inside the collector well with dopant type opposite from that of the collector well with interconnections to other

parts via electrode similar to the emitter regions of the high voltage bipolar transistor, or the source of the high voltage MOSFET;

an emitter, either as semiconductor of the same type as the collector at much higher doping density (for normal diode), or as barrier metal silicide (for Schottky diode); and

the base and collector terminal are connected and serving as the cathode while the emitter is serving as the anode of the diode.

Preferably, the collector well of for the diode connected bipolar shares the same mask for fabricating the wells for the body and base regions of the high voltage MOSFET and high voltage bipolar transistor, or as a separate region fabricated by additional masking.

Preferably, the collector well of for the diode connected bipolar has high doping density regions guarding a low doping density region of the same type with a junction depth less than the high doping region. The high doping regions are used for withstanding the high breakdown voltage as well as connecting the low doping density collector well for making connection. The low doping density region serves as the actual collector well inside which the base and emitter of the diode connected bipolar device are formed.

Preferably, the wells for the body of the high voltage MOSFET and the base of the high voltage bipolar transistor are merged for the case in which the body of the high voltage MOSFET is electrically connected to the base of the high voltage bipolar transistor. In addition, semi-super-junction columns between the high voltage MOSFET and the high voltage bipolar transistor can also be merged, with the isolation region between them eliminated.

Preferably, the diode is a Schottky diode and connections to semiconductor regions other than the Schottky diode anode are made via barrier metal silicide.

Preferably, connections to the base region of the high voltage bipolar transistor and the body region of the high voltage MOSFET, and the collector region of the diode connected bipolar device using normal base emitter junction are made via the same kind of semiconductor electrode for the anode of the diode.

BRIEF DESCRIPTION OF THE DRAWINGS

Preferred forms of the present invention will now be described by way of example with reference to the accompanying drawings, wherein:

FIG. 1 shows a typical prior art switching converter with isolated constant voltage output;

FIG. 2 shows a typical prior art switching converter with non-isolated constant current output for LED lighting application;

FIG. 3 illustrates two typical prior art circuit schematic for Darlington transistor with three pin package;

FIG. 4 is a schematic circuit diagram for the invented three pin high voltage Darlington bipolar power switching device with fast turn off time;

FIG. 5 illustrates a possible bonding diagram to integrate discrete devices forming the invented high voltage Darlington bipolar power switching device into a single three pin package;

FIG. 6 illustrates another possible bonding diagram to integrate discrete devices forming the invented high voltage Darlington bipolar power switching device into a single three pin package;

FIG. 7 illustrates a possible cross section of the invented high voltage Darlington bipolar switching device as a monolithic IC;

FIG. 8 illustrates another possible cross section of the invented high voltage Darlington bipolar switching device as a monolithic IC;

FIG. 9 illustrates a third possible cross section of the invented high voltage Darlington bipolar switching device as a monolithic IC;

FIG. 10 illustrates another possible cross section for the structure of the diode connected bipolar device up to the forming of the base region;

FIG. 11 is a schematic circuit diagram for the invented three pin high voltage hybrid MOSFET/bipolar power switching device with fast turn off time;

FIG. 12 illustrates a possible bonding diagram to integrate discrete devices forming the invented high voltage hybrid/bipolar power switching device into a single three pin package;

FIG. 13 illustrates a possible cross section of the invented high voltage hybrid MOSFET/bipolar switching device as a monolithic IC using modified high voltage planer VDMOS process;

FIG. 14 illustrates another possible cross section of the invented high voltage hybrid MOSFET/bipolar switching device as a monolithic IC using modified high voltage planer VDMOS process;

FIG. 15 illustrates a third possible cross section of the invented high voltage hybrid MOSFET/bipolar switching device as a monolithic IC using modified high voltage planer VDMOS process;

FIG. 16 illustrates a possible cross section of the invented high voltage hybrid MOSFET/bipolar switching device as a monolithic IC using modified high voltage super-junction VDMOS process;

FIG. 17 illustrates another possible cross section of the invented high voltage hybrid MOSFET/bipolar switching device as a monolithic IC using modified high voltage super-junction VDMOS process;

FIG. 18 illustrates a possible cross section of the invented high voltage hybrid MOSFET/bipolar switching device as a monolithic IC using modified high voltage semi-super-junction VDMOS process;

FIG. 19 illustrates another possible cross section of the invented high voltage hybrid MOSFET/bipolar switching device as a monolithic IC using modified high voltage semi-super-junction VDMOS process;

DETAILED DESCRIPTION

FIG. 4 is a schematic circuit diagram for an embodiment of the invented three pin high voltage Darlington bipolar power switching device with fast turn off time. High voltage bipolar transistors **401** and **402** form a conventional Darlington bipolar transistor. The current gain of the Darlington transistor is the product of the individual current gain of transistor **401** and transistor **402**. Typical current gain of 100 to 400 can be achieved. Therefore, base current to turn on the Darlington transistor is small and the associated power is comparable to the gate drive for power MOSFET power switching device for handling the same output power level. The addition of the diode **403** is to provide a discharging path for the base of transistor **402** during switch off of the Darlington transistor. Hence, diode **403** ensures fast base relaxation and thus fast turn off of this invented power switching device. For diode **403**, Schottky diode is more preferred due to the low forward voltage as compared with the forward voltage of the base emitter junction of transistor **402**. This enables the direct connecting of the emitter terminal of the switching device to Vss. A normal diode can still work due to the emitter voltage

in typical applications is higher than the Vss voltage as in the cases of FIG. 1 and FIG. 2. Hence, this invented power switching device can be used with the collector and emitter terminals as the positive and negative sides of the power switching device while the base terminal as the control terminal in FIG. 1 and FIG. 2.

The three discrete semiconductor chips forming the invented high voltage Darlington bipolar power switching devices can be packaged into a single three pin IC. Bipolar transistors used are having the backside substrate as the collector terminal while the base and emitter terminals are at the front side with bonding pads. Diode having cathode as substrate and anode pad at front side is used. The two bipolar transistors are die attached to the main die pad using conductive die attach epoxy. The main die pad and the collector pin of the package are electrically connected. The diode is conductive die attached to the base pin. Appropriate bonding connects the three individual discrete semiconductor chips into the circuit as shown in FIG. 4. Further steps such as plastic moulding, etc., to complete the packaging are then carried out to complete the three pin packaging. FIG. 5 is a bonding diagram for inter-connecting the discrete devices into a single three pin package.

It should be noted that if high voltage Darlington bipolar transistor chip with four bonding pads, namely collector, emitter, first and inner base pads, are available, the two bipolar chips in FIG. 5 can be reduced to a single chip and the inter-chip bonding wire between the first emitter and the second base can be eliminated. The new bonding diagram for this particular embodiment is illustrated in FIG. 6.

The three discrete devices forming the invented high voltage Darlington bipolar power switching device can be fabricated as a monolithic integrated circuit (IC). Use of high voltage SOI process is an obvious embodiment. Other possible embodiments are discussed in subsequent paragraphs.

The major difficulty in integrating the three discrete devices forming the invented high voltage Darlington power switching device into a monolithic IC using high voltage planer process is the isolation of the diode from the substrate. A simple diode using a base well as anode and the emitter electrode inside the base well as cathode will not work due to the turn on of the parasitic vertical bipolar transistor having the substrate acting as the collector in the same way as for the transistors forming the high voltage Darlington transistor. A diode connected bipolar is used to provide means to avoid the turn on of the parasitic transistor in the diode region.

FIG. 7 is a cross section of a possible embodiment of such an integrated circuit. In FIG. 7, N+ region **701** at the back side is used for conductive die attach to the die pad which is also electrically serving as the collector pin, the N- region **702** is the actual collector region that can withstand high breakdown voltage. P well **703** is the collector of a diode connected PNP transistor (**725**) inside which the N+ regions **707** serves as the base, while the P+ region **708** is the emitter. The emitter **708** serves as the anode while base formed by N+ region **707** together with P well collector **703** serve as the cathode of the diode connected PNP transistor **725**. The use of diode connected PNP transistor instead of a simple diode using the P well **703** as anode and N+ **707** as cathode is required due to the vertical NPN transistor **726** formed by N- region **702** as collector, P well region **703** as base, and N+ regions **707** as the emitter region, will become on during the time when current flows from the P well anode **703** to the N+ cathode **707**. This diode connected PNP transistor structure ensures that the vertical NPN transistor **726** will never be on due to the P well **703** serving as base is always at the same potential as the N+ emitter region **707** inside it. Furthermore, transistor current

gain makes this device smaller as compared with simple diode for handling the same forward diode current. The P well region of this diode connected device **725** may share the same masking, having the same dosage and drive in conditions as other P wells (**704** and **705**) serving as base regions for the 2 bipolar transistors forming the Darlington transistor, or may have another independent P well having another masking step, dosage and drive in conditions provided that it can together with the collector N- layer **702** to withstand the required high reverse breakdown voltage. P wells **704** and **705** are the base regions for the first and inner bipolar transistors (**727** and **728**) forming the Darlington transistor respectively. N+ regions **711** and **713** are the emitters for the first bipolar transistor for the Darlington transistor while N+ regions **716**, **718**, **721**, and **723** are the emitters for the inner bipolar transistor of the Darlington transistor. All such N+ emitters may and prefer to share the same masking, and have the same dosage as the N+ region **707** (cathode of the diode connected PNP described previously). The dopant density of P wells **703**, **704** and **705** are usually high enough for making direct ohmic contact with metal. Since an extra masking step is required for making the P+ junction **708**, this provides an option to share the same mask to make P+ contacts for metal layer to connect to these three P well regions. Since P well **703** and P well **704** are at the same potential (electrically connected), it is preferred to merge these two P wells into a single P well in order to reduce the chip size.

FIG. **8** depicts another embodiment in which devices **832**, **833**, **834** and **835** correspond to devices **725**, **726**, **727**, and **728** respectively in FIG. **7**. The major difference between FIG. **7** and FIG. **8** is the implementation of the diode connected bipolar transistor. The diode connected bipolar transistor **832** in FIG. **8** has a Schottky base emitter junction while the corresponding device **725** in FIG. **7** is having a normal base emitter junction. An additional masking step is required to create the N- junction inside P well **803**, which can have a deeper or shallower junction depth as compared with the N+ junctions. Interconnecting metal contact via the barrier metal silicide **809** for connecting to the N- region inside the P well **803** is used to form the Schottky junction. It is optional for the interconnecting metal to make contact to other semiconductor regions direct, or via the barrier metal silicide (**810**, **811**, **814**, **815**, **816**, **817**, **818**, **819**, **821**, **822**, **824**, **825**, **826**, **828**, **829**, **831** and **836**). Making connection for other regions via barrier metal silicide has the possibility to save 1 masking step. Since P well **803** and P well **804** are at the same potential (electrically connected), it is preferred to merge these two P wells into a single P well in order to reduce the chip size.

Another embodiment is to change the diode connected transistor's base emitter junction in FIG. **8** to a bulk silicon P+ junction. The actual equivalent circuit is the same as for FIG. **7**. Cross section of such a monolithic device is illustrated in FIG. **9**. Options applicable to FIG. **7** are applicable to FIG. **9** in general.

Since the wells for the collector of the diode connected bipolar device as well as the base region of the Darlington device are of relatively high doping concentration, the process control for forming a lightly doped inversed region inside the diode connected bipolar device's collector well is very tight. To alleviate the tight processing control requirements, FIG. **10** illustrates a cross section of device structure up to the forming the base region of the diode connected bipolar device. Further structures to complete the cross section (for either normal bipolar or Schottky bipolar) are similar to those shown in FIG. **8** and FIG. **9**. In FIG. **10**, the collector region **1005** for the diode connected bipolar is having much lower dopant concentration as compared with P well region **1003**

and **1004** that shield off region **1005** from high voltage. Hence, a lightly doped base region **1006** can be fabricated without tight processing control. P well **1003** together with **1004**, and the high voltage collector region **1002** will have pinch off below region **1005** during the time when region **1001** is at high voltage. This ensures breakdown will not occur at region **1005**. Such diode connected bipolar structures can be used to replace the equivalent parts in FIG. **8** and FIG. **9**.

FIG. **11** is the circuit diagram for an embodiment of the invented three pin high voltage hybrid MOSFET/bipolar power switching device with fast turn off time. Basically, this is the replacing of the first bipolar transistor of the circuit in FIG. **4** by a MOSFET such that the circuit is IGBT in nature. Similar to diode **403**, diode **1103** provides the base relaxation path during the turn off of the power switching device to ensure fast switching off time. Again, a Schottky diode is preferred while a normal diode can function.

The three discrete semiconductor chips forming the invented high voltage hybrid MOSFET/bipolar power switching device can be packaged into a single three pin IC. MOSFET and bipolar transistor used are having the backside substrate as the drain and collector terminals respectively while other terminals are at the front side with bonding pads. Diode having cathode as substrate and anode pad at front side is used. The MOSFET and the bipolar transistor are die attached to the main die pad using conductive die attach epoxy. The main die pad and the collector pin of the package are electrically connected. The diode is conductive die attached to the base pin. Appropriate bonding connects the three individual discrete semiconductor chips into the circuit as shown in FIG. **11**. Further steps such as plastic moulding, etc., to complete the packaging are then carried out to complete the three pin packaging. FIG. **12** illustrates the bonding diagram for inter-connecting the discrete devices into a single three pin package.

The three discrete devices forming the invented high voltage hybrid MOSFET/bipolar power switching device can be fabricated as a monolithic integrated circuit (IC). Use of high voltage SOI process is an obvious embodiment. Other possible embodiments are discussed in subsequent paragraphs.

The major difficulty in integrating the three discrete devices forming the invented high voltage hybrid MOSFET/bipolar power switching device into a monolithic IC using high voltage planar, super-junction, or semi-super-junction processes is the isolation of the diode from the substrate. A simple diode using a base well as anode and the emitter electrode inside the base well as cathode will not function due to the turn on of the vertical high voltage bipolar transistor having the substrate acting as the collector in the same way as for the vertical high voltage bipolar transistor. Similar to the high voltage Darlington power switching device, a diode connected bipolar is used to provide means to avoid the turn on of the parasitic transistor in the diode region.

FIG. **13** illustrates a possible cross section of a monolithic device integrating the three devices, namely a high voltage MOSFET, a high voltage bipolar transistor, and a diode, to form the invented high voltage hybrid MOSFET/bipolar switching device using high voltage planar process. The N-substrate **1302** serves as the drain and collector for the high voltage MOSFET **1327** and the high voltage bipolar transistor **1328** respectively. It is connected to the collector terminal of the switching device via the N+ backside **1301**. P well **1305** serves as the base region while N+ electrodes **1316**, **1318**, **1321**, and **1323** serve as the emitter electrodes for high voltage bipolar transistor **1328**. P+ electrodes **1315**, **1317**, **1319**, **1320**, **1322**, and **1324** are optional electrodes for making

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metal contact to the base region **1305** of the high voltage bipolar transistor. P well **1304** serves as the body region while N+ electrodes **1311** and **1313** serve as the source electrode, and the poly silicon **1310** and **1314** having thin oxide over channel region and thick oxide over field region serve as gate electrodes for the high voltage MOSFET **1327**. P+ electrode **1312** is the optional electrode for making metal contact to the body region **1304** of the high voltage MOSFET **1327**. P well **1303** is the collector for the diode connected bipolar **1325**. N+ electrode **1307** is the base electrode inside P well **1303** while P+ electrode **1308** serves as the emitter electrode inside base region **1307**. Emitter **1308** serves as the anode of the diode while base **1307** and collector **1303** are connected together by metal serve as the cathode of the diode. The main substrate **1302**, P well **1303** and N+ electrode **1307** form a parasitic bipolar **1326** at the location while where the diode connected bipolar **1325** is located. Since the base emitter junction (**1303** and **1307**) of device **1326** is metal connected as required by the diode connected bipolar **1325**, the turn on of the parasitic bipolar **1326** is prevented. The source and body of the high voltage MOSFET **1327** is connected to the base of the high voltage bipolar transistor **1328**, as well as to the anode of the diode connected bipolar **1325**. The gate of the high voltage MOSFET **1327** is connected to the cathode of the diode connected bipolar **1325**, and is also serving as the gate terminal of the switching device. The emitter terminal of the high voltage bipolar transistor **1328** serves as the emitter terminal of the switching device. P+ electrodes **1306**, **1309**, **1312**, **1315**, **1317**, **1319**, **1320**, **1322**, and **1324** are optional connecting electrodes for making metal contact to the P well **1303**, **1304**, and **1305**. Optionally, instead of connecting the body of the high voltage MOSFET to its own source electrode, it is also possible to connect the body to the emitter of the high voltage bipolar **1328**, although the former connection is preferred. If the body of the high voltage MOSFET **1327** is connected to its own source, since it is electrically having the same potential as the base of the high voltage bipolar transistor **1328**, P well **1304** and P well **1305** can then be merged as a single well to save chip area.

FIG. 14 illustrates another possible cross section of a monolithic device integrating the three devices, namely a high voltage MOSFET, a high voltage bipolar transistor, and a diode, to form the invented high voltage hybrid MOSFET/bipolar switching device by high voltage planer process. The substrate **1402** serves as the drain and collector for the high voltage MOSFET **1437** and the high voltage bipolar transistor **1438** respectively. It is connected to the collector terminal of the switching device via the N+ backside **1401**. P well **1405** serves as the base region while N+ electrodes **1421**, **1422**, **1423**, and **1424** serve as the emitter electrodes for high voltage bipolar transistor **1438**. P well **1404** serves as the body region while N+ electrodes **1412** and **1413** serve as the source electrodes, and the poly-silicon electrodes **1415** and **1419** having thin oxide over channel region and thick oxide over field region serve as gate electrodes for the high voltage MOSFET **1437**. P well **1403** is the collector for the diode connected bipolar **1435**. N- electrode **1407** is the base electrode inside P well **1403** while the barrier metal silicide electrode **1410** serves as the emitter electrode inside base region **1407** (N- electrode **1407** and barrier metal silicide **1410** form the Schottky base emitter junction). Connection to the base region **1407** is made via N+ electrodes **1406** and **1408**. Emitter **1410** serves as the anode of the diode while base **1407** and collector **1403** are connected together serve as the cathode of the diode. Barrier metal silicide electrodes **1409**, **1411**, **1414**, **1416**, **1417**, **1418**, **1420**, **1425**, **1426**, **1427**, **1428**, **1429**, **1430**, **1431**, **1432**, **1433**, and **1434** are preferred optional electrodes

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for making metal contacts to the semiconductor electrodes other than the emitter electrode of the diode connected bipolar **1435**.

Direct metal connections to these electrodes are possible but the former case is preferred due to the possibility to share the same masking step for metal with the barrier metal silicide. The main N- substrate **1402**, P well **1403** and N- electrode **1407** form a parasitic bipolar **1436** at the location while where the diode connected bipolar **1435** is located. Since the base emitter junction (**1403** and **1407**) of device **1436** is shorted as required by the diode connected bipolar **1435**, the turn on of the parasitic bipolar **1436** is prevented. The source and body of the high voltage MOSFET **1437** is connected to base of the high voltage bipolar transistor **1438**, as well as to the anode of the diode connected bipolar **1435**. The gate of the high voltage MOSFET **1437** is connected to the cathode of the diode connected bipolar **1435**, and is also serving as the gate terminal of the switching device. The emitter terminal of the high voltage bipolar transistor **1438** serves as the emitter terminal of the switching device. Optionally, instead of connecting the body of the high voltage MOSFET **1437** to its own source electrode, it is also possible to connect the body to the emitter of the high voltage bipolar **1438**, although the former connection is preferred. If the body of the high voltage MOSFET **1437** is connected to its own source, since it is electrically having the same potential as the base of the high voltage bipolar transistor **1438**, P well **1404** and P well **1305** can then be merged as a single well to save chip area.

FIG. 15 illustrates another possible cross section of a monolithic device integrating the three devices, namely a high voltage MOSFET, a high voltage bipolar transistor, and a diode, to form the invented high voltage hybrid MOSFET/bipolar switching device by high voltage planer process. The substrate **1502** serves as the drain and collector for the high voltage MOSFET **1529** and the high voltage bipolar transistor **1530** respectively. It is connected to the collector terminal of the switching device via the N+ backside **1501**. P well **1505** serves as the base region while N+ electrodes **1518**, **1520**, **1523**, and **1525** serve as the emitter electrodes for high voltage bipolar transistor **1530**. P well **1504** serves as the body region while N+ electrodes **1512** and **1514** serve as the source electrodes, and the poly-silicon electrodes **1515** and **1516** having thin oxide over channel region and thick oxide over field region serve as gate electrodes for the high voltage MOSFET **1529**. P well **1503** is the collector for the diode connected bipolar **1527**. N- electrode **1508** is the base electrode inside P well **1503** while the P+ electrode **1511** serves as the emitter electrode inside base region **1508**. Connection to the base region **1508** is made via N+ electrodes **1507** and **1509**. Emitter **1511** serves as the anode of the diode while base **1508** and collector **1503** are connected together serve as the cathode of the diode. P+ electrodes **1506**, **1510**, **1513**, **1517**, **1519**, **1521**, **1522**, **1524**, and **1526** are optional electrodes for making metal contacts to P wells **1503**, **1504** and **1505** while direct metal connections to these P wells is possible. The main N- substrate **1502**, P well **1503** and N-electrode **1508** form a parasitic bipolar **1528** at the location where the diode connected bipolar **1527** is located. Since the base emitter junction (**1503** and **1508**) of device **1527** is metal connected as required by the diode connected bipolar **1527**, the turn on of the parasitic bipolar **1528** is prevented. The source and body of the high voltage MOSFET **1529** is connected to base of the high voltage bipolar transistor **1530**, as well as to the anode of the diode connected bipolar **1527**. The gate of the high voltage MOSFET **1529** is connected to the cathode of the diode connected bipolar **1527**, and is also

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serving as the gate terminal of the switching device. The emitter terminal of the high voltage bipolar transistor **1530** serves as the emitter terminal of the switching device. Optionally, instead of connecting the body of the high voltage MOSFET **1529** to its own source electrode, it is also possible to connect the body of the high voltage MOSFET **1529** to the emitter of the high voltage bipolar **1530**, although the former connection is preferred. If the body of the high voltage MOSFET **1529** is connected to its own source, since it is electrically having the same potential as the base of the high voltage bipolar transistor **1530**, P well **1504** and P well **1505** can then be merged as a single well to save chip area.

Since the wells for the collector of the diode connected bipolar device, the body of the high voltage MOSFET and the base region of the high voltage bipolar transistor are of relatively high doping concentration, the process control for forming a lightly doped inverted region inside the diode connected bipolar device's collector well is very tight. The way to alleviate this problem is illustrated in FIG. **10** and had been discussed. Further structures to complete the cross section (for either normal bipolar or Schottky bipolar) are similar to those shown in FIG. **14** and FIG. **15**. Such diode connected bipolar structures can be used to replace the equivalent parts in FIG. **14** and FIG. **15**.

FIG. **16** illustrates another possible cross section of a monolithic device integrating the three devices, namely a high voltage MOSFET, a high voltage bipolar transistor, and a diode, to form the invented high voltage hybrid MOSFET/bipolar switching device by high voltage super-junction process. The N⁻ substrate **1611** serves as the drain for the high voltage MOSFET **1647** while N⁻ substrate regions **1613** and **1614** serve as the collector of the high voltage bipolar transistor **1648**. These N⁻ regions are connected to the collector terminal of the switching device via the N⁺ backside **1601**. Super-junction P⁺ columns **1602**, **1603**, **1604**, **1605**, **1606**, **1607** and **1608** are used together with N⁻ substrate regions **1609**, **1610**, **1611**, **1612**, **1613** and **1614** to withstand the high breakdown voltage. P wells **1618** and **1619** serve as the base region while N⁺ electrodes **1625**, **1626**, **1627**, and **1628** serve as the emitter electrodes for high voltage bipolar transistor **1648**. P wells **1616** and **1617** serve as the body regions while N⁺ electrodes **1623** and **1624** serve as the source electrodes, and the poly-silicon electrode **1633** having thin oxide over channel region and thick oxide over field region serve as gate electrode for the high voltage MOSFET **1647**. P well **1615** is the collector for the diode connected bipolar **1645**. N⁻ electrode **1621** is the base electrode inside P well **1615** while the barrier metal silicide electrode **1630** serves as the emitter electrode inside base region **1621** (N⁻ well **1621** and barrier metal silicide **1630** form a Schottky base emitter junction). Connection to the base region **1621** is made via N⁺ electrodes **1620** and **1622**. Emitter **1630** serves as the anode of the diode while base **1621** and collector **1615** are connected together serve as the cathode of the diode. Barrier metal silicide electrodes **1629**, **1631**, **1632**, **1634**, **1635**, **1636**, **1637**, **1638**, **1639**, **1640**, **1641**, **1642**, **1643**, and **1644** are preferred optional barrier metal silicide electrodes for making metal contacts to the semiconductor electrodes other than the emitter electrode of the diode connected bipolar **1645**. Direct metal connections to these electrodes are possible but the former case is preferred due to the possibility to share the same masking step for metal with the barrier metal silicide. The N⁻ substrate **1609**, P well **1615** and N⁻ electrode **1621** form a parasitic bipolar **1646** at the location where the diode connected bipolar **1645** is located. Since the base emitter junction (**1615** and **1621**) of device **1646** is shorted as

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required by the diode connected bipolar **1645**, the turn on of the parasitic bipolar **1646** is prevented.

The source and body of the high voltage MOSFET **1647** are connected to base of the high voltage bipolar transistor **1648**, as well as to the anode of the diode connected bipolar **1645**. The gate of the high voltage MOSFET **1647** is connected to the cathode of the diode connected bipolar **1645**, and is also serving as the gate terminal of the switching device. The emitter electrodes of the high voltage bipolar transistor **1648** serve as the emitter terminal of the switching device. Optionally, instead of connecting the body of the high voltage MOSFET **1647** to its own source electrode, it is also possible to connect the body to the emitter of the high voltage bipolar **1648**, although the former connection is preferred. If the body of the high voltage MOSFET **1647** is connected to its own source, since it is electrically having the same potential as the base of the high voltage bipolar transistor **1648**, P wells **1617**, **1618** and **1619** can then be merged as a single well to save chip area. Hence, super-junction columns **1605** and **1606** can be merged to eliminate the N⁻ region **1612** for isolation purpose between them.

FIG. **17** illustrates the cross section of another possible monolithic device integrating the 3 devices, namely a high voltage MOSFET, a high voltage bipolar transistor, and a diode, to form the invented high voltage hybrid MOSFET/bipolar switching device by high voltage super-junction process. The N⁻ substrate **1711** serves as the drain for the high voltage MOSFET **1739**. N⁻ substrate regions **1713** and **1714** serve as base for the high voltage bipolar transistor **1740**. These N⁻ regions are connected to the collector terminal of the switching device via the N⁺ backside **1701**. Super-junction P⁺ columns **1702**, **1703**, **1704**, **1705**, **1706**, **1707** and **1708** are used together with N⁻ substrate regions to withstand the high breakdown voltage. P wells **1718** and **1719** serve as the base region while N⁺ electrodes **1725**, **1726**, **1727**, and **1728** serve as the emitter electrodes for high voltage bipolar transistor **1740**. P wells **1716** and **1717** serve as the body regions while N⁺ electrodes **1723** and **1724** serve as the source electrodes, and the poly-silicon electrode **1736** having thin oxide over channel region and thick oxide over field region serves as gate electrode for the high voltage MOSFET **1739**. P well **1715** is the collector for the diode connected bipolar **1737**. N-electrode **1721** is the base electrode inside P well **1715** while the P⁺ electrode **1729** serves as the emitter electrode inside base region **1721**. Connection to the base region **1721** is made via N⁺ electrodes **1720** and **1722**. Emitter **1729** serves as the anode of the diode while base **1721** and collector **1715** are connected together to serve as the cathode of the diode. The N-substrate **1709**, P well **1715** and N⁻ electrode **1721** form a parasitic bipolar **1738** at the location where the diode connected bipolar **1737** is located. Since the base emitter junction (**1715** and **1721**) of device **1738** is metal connected as required by the diode connected bipolar **1737**, the turn on of the parasitic bipolar **1738** is prevented. P⁺ electrodes **1730**, **1731**, **1732**, **1733**, **1734**, and **1735** are optional electrodes for making metal contacts to P wells **1718** and **1719** while direct metal connections to these P wells is possible. The source and body of the high voltage MOSFET **1739** are connected to base of the high voltage bipolar transistor **1740**, as well as to the anode of the diode connected bipolar **1737**. The gate of the high voltage MOSFET **1739** is connected to the cathode of the diode connected bipolar **1737**, and is also serving as the gate terminal of the switching device. The emitter electrodes of the high voltage bipolar transistor **1740** serve as the emitter terminal of the switching device. Optionally, instead of connecting the body of the high voltage MOSFET **1739** to its own source electrode, it is also

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possible to connect the body of the high voltage MOSFET **1739** to the emitter of the high voltage bipolar **1740**, although the former connection is preferred. If the body of the high voltage MOSFET **1739** is connected to its own source, since it is electrically having the same potential as the base of the high voltage bipolar transistor **1740**, P wells **1717**, **1718** and **1719** can then be merged as a single well to save chip area. Hence, super-junction columns **1705** and **1706** can be merged to eliminate the N- region **1712** for isolation purpose between them.

Since the wells for the collector of the diode connected bipolar device, the body of the high voltage MOSFET and the base region of the high voltage bipolar transistor are of relatively high doping concentration, the process control for forming a lightly doped inversed region inside the diode connected bipolar device's collector well is very tight. The way to alleviate this problem is illustrated in FIG. **10** and had been discussed. Further structures to complete the cross section (for either normal bipolar or Schottky bipolar) are similar to those shown in FIG. **16** and FIG. **17**. Such diode connected bipolar structures can be used to replace the equivalent parts in FIG. **16** and FIG. **17**.

FIG. **18** illustrates another possible cross section of a monolithic device integrating the three devices, namely a high voltage MOSFET, a high voltage bipolar transistor, and a diode, to form the invented high voltage hybrid MOSFET/ bipolar switching device by high voltage semi-super-junction process. The N- substrate **1802** serves as the drain for the high voltage MOSFET **1842** and the collector for the high voltage bipolar transistor **1843**. The N- substrate **1802** is connected to the collector terminal of the switching device via the N+ backside **1801**. Semi-super-junction P+ columns **1803**, **1804**, **1805**, **1806**, **1807**, **1808** and **1809** are used together with N- substrate **1802** to withstand the high breakdown voltage. P wells **1813** and **1814** serve as the base regions while N+ electrodes **1820**, **1821**, **1822**, and **1823** serve as the emitter electrodes for high voltage bipolar transistor **1843**. P wells **1811** and **1812** serve as the body regions while N+ electrodes **1818** and **1819** serve as the source electrodes, and the poly-silicon electrode **1828** having thin oxide over channel region and thick oxide over field region serve as gate electrode for the high voltage MOSFET **1842**. P well **1810** is the collector for the diode connected bipolar **1840**. N- electrode **1816** is the base electrode inside P well **1810** while the barrier metal silicide electrode **1825** serves as the emitter electrode inside base region **1816** (N- well **1816** and barrier metal silicide **1825** form a Schottky base emitter junction). Connection to the base region **1816** is made via N+ electrodes **1815** and **1817**. Emitter **1825** serves as the anode of the diode while base **1816** and collector **1810** are connected together serve as the cathode of the diode. Barrier metal silicide electrodes **1824**, **1826**, **1827**, **1829**, **1830**, **1831**, **1832**, **1833**, **1834**, **1835**, **1836**, **1837**, **1838**, and **1839** are preferred optional barrier metal silicide electrodes for making metal contacts to the semiconductor electrodes other than the emitter electrode of the diode connected bipolar **1840**. Direct metal connections to these electrodes are possible but the former case is preferred due to the possibility to share the same masking step for metal with the barrier metal silicide. The N- substrate **1802**, P well **1810** and N- electrode **1816** form a parasitic bipolar **1841** at the location where the diode connected bipolar **1840** is located. Since the base emitter junction (**1810** and **1816**) of device **1841** is shorted as required by the diode connected bipolar **1840**, the turn on of the parasitic bipolar **1841** is prevented. The source and body of the high voltage MOSFET **1842** are connected to base of the high voltage bipolar transistor **1843**, as well as to the

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anode of the diode connected bipolar **1840**. The gate of the high voltage MOSFET **1842** is connected to the cathode of the diode connected bipolar **1840**, and is also serving as the gate terminal of the switching device. The emitter electrodes of the high voltage bipolar transistor **1843** serve as the emitter terminal of the switching device. Optionally, instead of connecting the body of the high voltage MOSFET **1842** to its own source electrode, it is also possible to connect the body to the emitter of the high voltage bipolar **1843**, although the former connection is preferred. If the body of the high voltage MOSFET **1842** is connected to its own source, since it is electrically having the same potential as the base of the high voltage bipolar transistor **1843**, P wells **1812**, **1813** and **1814** can then be merged as a single well to save chip area. Hence, super-junction columns **1806** and **1807** can be merged to eliminate the N- region for isolation purpose between them.

FIG. **19** illustrates the cross section of another possible monolithic device integrating the 3 devices, namely a high voltage MOSFET, a high voltage bipolar transistor, and a diode, to form the invented high voltage hybrid MOSFET/ bipolar switching device by high voltage semi-super-junction process. The N- substrate **1902** serves as the drain for the high voltage MOSFET **1934** and the collector for the high voltage bipolar transistor **1935**. The N- substrate **1902** is connected to the collector terminal of the switching device via the N+ backside **1901**. Semi-super-junction P+ columns **1903**, **1904**, **1905**, **1906**, **1907**, **1908** and **1909** are used together with N-substrate **1902** to withstand the high breakdown voltage.

P wells **1913** and **1914** serve as the base regions while N+ electrodes **1920**, **1921**, **1922**, and **1923** serve as the emitter electrodes for high voltage bipolar transistor **1935**. P wells **1911** and **1912** serve as the body regions while N+ electrodes **1918** and **1919** serve as the source electrodes, and the poly-silicon electrode **1925** having thin oxide over channel region and thick oxide over field region serves as gate electrode for the high voltage MOSFET **1934**. P well **1910** is the collector for the diode connected bipolar **1932**. N- electrode **1916** is the base electrode inside P well **1910** while the P+ electrode **1924** serves as the emitter electrode inside base region **1916**. Connection to the base region **1916** is made via N+ electrodes **1915** and **1917**. Emitter **1924** serves as the anode of the diode while base **1916** and collector **1910** are connected together to serve as the cathode of the diode. The N- substrate **1902**, P well **1910** and N- electrode **1916** form a parasitic bipolar **1933** at the location where the diode connected bipolar **1932** is located. Since the base emitter junction (**1910** and **1916**) of device **1933** is metal connected as required by the diode connected bipolar **1932**, the turn on of the parasitic bipolar **1933** is prevented. P+ electrodes **1926**, **1927**, **1928**, **1929**, **1930**, and **1931** are optional electrodes for making metal contacts to P wells **1913** and **1914** while direct metal connections to these P wells is possible. The source and body of the high voltage MOSFET **1934** are connected to base of the high voltage bipolar transistor **1935**, as well as to the anode of the diode connected bipolar **1932**. The gate of the high voltage MOSFET **1934** is connected to the cathode of the diode connected bipolar **1932**, and is also serving as the gate terminal of the switching device.

The emitter electrodes of the high voltage bipolar transistor **1935** serve as the emitter terminal of the switching device. Optionally, instead of connecting the body of the high voltage MOSFET **1934** to its own source electrode, it is also possible to connect the body of the high voltage MOSFET **1934** to the emitter of the high voltage bipolar **1935**, although the former connection is preferred. If the body of the high voltage MOSFET **1934** is connected to its own source, since it is electrically

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cally having the same potential as the base of the high voltage bipolar transistor **1935**, P wells **1912, 1913** and **1914** can then be merged as a single well to save chip area. Hence, semi-super-junction columns **1906** and **1907** can be merged to eliminate the N-region between them.

Since the wells for the collector of the diode connected bipolar device, the body of the high voltage MOSFET and the base region of the high voltage bipolar transistor are of relatively high doping concentration, the process control for forming a lightly doped inversed region inside the diode connected bipolar device's collector well is very tight. The way to alleviate this problem is illustrated in FIG. **10** and had been discussed. Further structures to complete the cross section (for either normal bipolar or Schottky bipolar) are similar to those shown in FIG. **18** and FIG. **19**. Such diode connected bipolar structures can be used to replace the equivalent parts in FIG. **18** and FIG. **19**.

The invention claimed is:

1. A monolithic three terminal high voltage Darlington bipolar power switching semiconductor integrated circuit having a base terminal and an emitter terminal including:

first and second high voltage bipolar transistors having base regions with wells and each having a base, with their substrates as a common collector and the collector terminal of the integrated circuit at a back side;

two semiconductor well regions with an opposite dopant type to the substrate serving as the base regions for the high voltage bipolar transistors;

high doping density semiconductor electrodes of the same type as the substrate inside the base regions serving as emitters for the high voltage bipolar transistors; wherein:

the base of the first high voltage bipolar transistor serves as the base terminal of the power switching integrated circuit;

the emitter of the first high voltage bipolar transistor connects to the base of the second high voltage bipolar transistor (inner base);

the emitter of the second high voltage bipolar transistor serves as the emitter terminal of the power switching integrated circuit; and

a diode having an anode and a cathode with its the anode connected to the inner base and the cathode connected to the base terminal of the power switching integrated circuit; wherein

the diode is a diode connected bipolar transistor with the following:

a collector as a well with opposite dopant type of the substrate on the substrate of the high voltage bipolar transistors;

a base inside the collector well with dopant type opposite to that of the collector well and interconnected to other components via high doping electrodes of the same type; an emitter, either as a semiconductor of the same type as the collector (for a normal diode), or as barrier metal silicide (for a Schottky diode); and

the base and collector terminal being mutually connected and serving as the cathode while the emitter serves as the anode of the diode.

2. The integrated circuit of claim **1**, further comprising a mask for fabricating the wells for the base regions and

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wherein the collector well for the diode connected bipolar shares the mask for fabricating the wells for the base regions of the two high voltage bipolar transistors, or is a separate region fabricated by additional masking.

3. The integrated circuit of claim **1**, wherein the collector well of the diode connected bipolar transistor has high doping density regions guarding a low doping density region of the same type with a junction depth less than the high doping regions, the high doping regions being used for withstanding a high breakdown voltage as well as connecting the low doping density collector well for making connection to other electrodes, the low doping density region is serving as the actual collector well inside which the base and emitter of the diode connected bipolar transistor are formed.

4. The integrated circuit of claim **1**, wherein the well for the collector of the diode connected bipolar transistor is merged with the base of the first high voltage bipolar transistor.

5. The integrated circuit of claim **1**, wherein a Schottky junction is used for the diode connected bipolar transistor and connections to semiconductor regions are made via barrier metal silicide.

6. The integrated circuit of claim **1**, being monolithic and wherein the diode connected bipolar transistor has a Schottky base emitter junction and connections to the Schottky diode anode make direct contact thereto.

7. The integrated circuit of claim **1**, wherein connections to the base regions of the high voltage bipolar transistors forming the Darlington device and the collector region of the diode connected bipolar transistor using a normal base emitter junction are made via a same kind of semiconductor electrode for the anode of the diode.

8. A three terminal high voltage hybrid MOSFET/bipolar transistor power switching device said MOSFET having channel terminals and a gate and said bipolar transistor having a collector, a base and an emitter, said power switching device having a collector terminal, an emitter terminal and a gate terminal including the following:

a high voltage MOSFET and a high voltage bipolar transistor, with the channel terminals of the MOSFET connected to the collector and base terminals of the bipolar transistor respectively, the collector and emitter of the bipolar transistor serving as the collector and emitter terminals of the switching device respectively, and the gate of the MOSFET serving as the gate terminal of the three terminal high voltage hybrid MOSFET/bipolar transistor power switching device; and

a diode having an anode and a cathode with the anode connected to the base of the high voltage bipolar transistor, and the cathode connected to the gate terminal of the power switching device.

9. The power switching device of claim **8**, wherein the diode is a Schottky diode.

10. The power switching device of claim **8**, wherein the diode is a diode connector bipolar transistor.

11. The power switching device of claim **8**, wherein all components are fabricated on a monolithic IC using a high voltage SOI process.

12. The power switching device of claim **8**, wherein all components are fabricated as a monolithic IC using a planer, super-junction, or semi-super-junction high voltage process.

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